



US009318584B2

(12) **United States Patent**  
**Cheng et al.**

(10) **Patent No.:** **US 9,318,584 B2**  
(45) **Date of Patent:** **Apr. 19, 2016**

(54) **ISOLATION SCHEME FOR BIPOLAR TRANSISTORS IN BICMOS TECHNOLOGY**

USPC ..... 257/565  
See application file for complete search history.

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(\* ) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

Notice of Allowance issued in U.S. Appl. No. 13/661,359 dated Aug. 22, 2014.

(Continued)

(21) Appl. No.: **14/492,582**

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(22) Filed: **Sep. 22, 2014**

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(65) **Prior Publication Data**

(57) **ABSTRACT**

US 2015/0041956 A1 Feb. 12, 2015

Device structures and design structures for a bipolar junction transistor. The device structure includes a collector region in a substrate, a plurality of isolation structures extending into the substrate and comprised of an electrical insulator, and an isolation region in the substrate. The isolation structures have a length and are arranged with a pitch transverse to the length such that each adjacent pair of the isolation structures is separated by a respective section of the substrate. The isolation region is laterally separated from at least one of the isolation structures by a first portion of the collector region. The isolation region laterally separates a second portion of the collector region from the first portion of the collector region. The device structure further includes an intrinsic base on the second portion of the collector region and an emitter on the intrinsic base. The emitter has a length transversely oriented relative to the length of the isolation structures.

**Related U.S. Application Data**

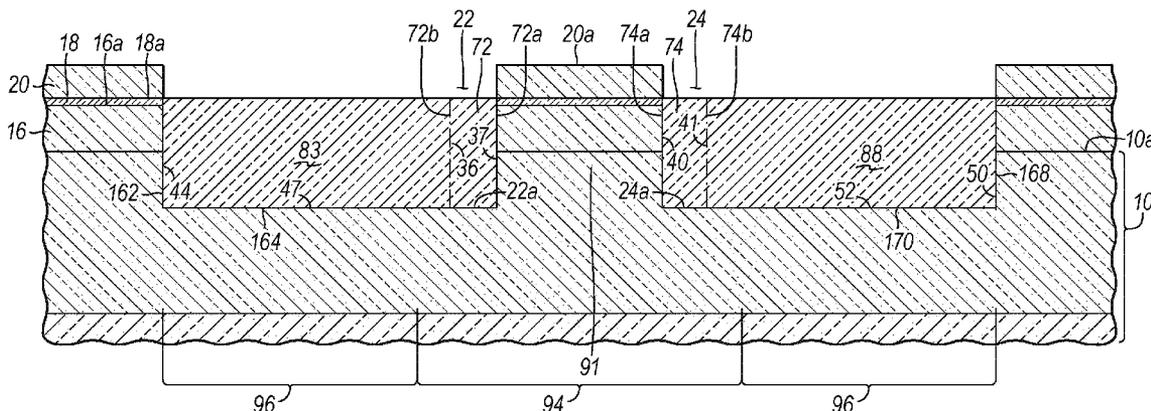
(62) Division of application No. 13/661,359, filed on Oct. 26, 2012, now Pat. No. 8,921,195.

(51) **Int. Cl.**  
**H01L 29/732** (2006.01)  
**H01L 29/66** (2006.01)  
**H01L 29/737** (2006.01)  
**H01L 21/762** (2006.01)

(52) **U.S. Cl.**  
CPC ..... **H01L 29/732** (2013.01); **H01L 21/76229** (2013.01); **H01L 21/76283** (2013.01); **H01L 29/66242** (2013.01); **H01L 29/7378** (2013.01)

(58) **Field of Classification Search**  
CPC ..... H01L 29/732; H01L 21/76229; H01L 21/76283; H01L 29/66242; H01L 29/7378

**19 Claims, 19 Drawing Sheets**



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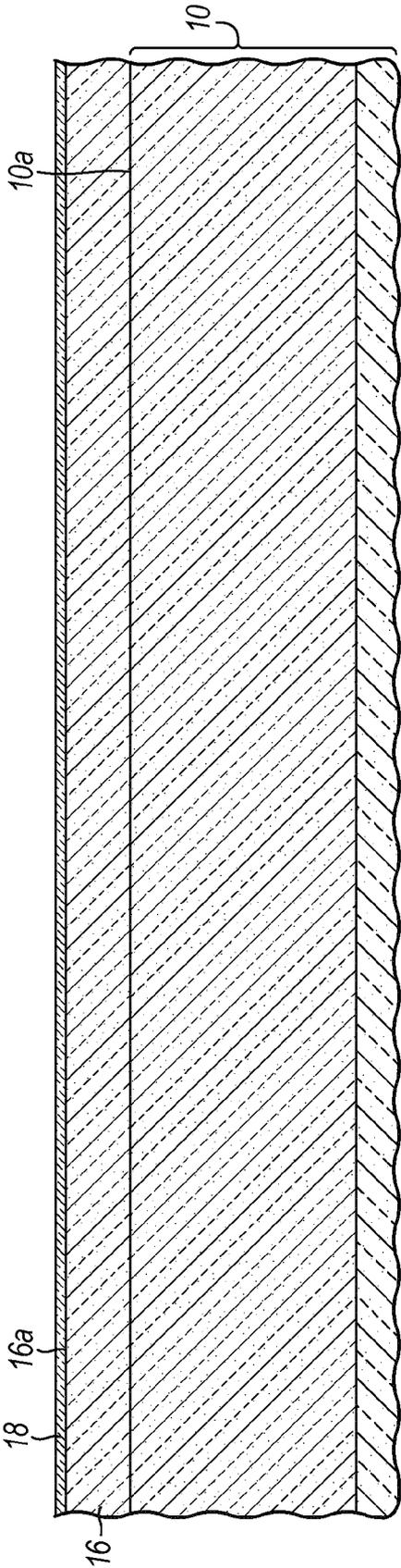


FIG. 1

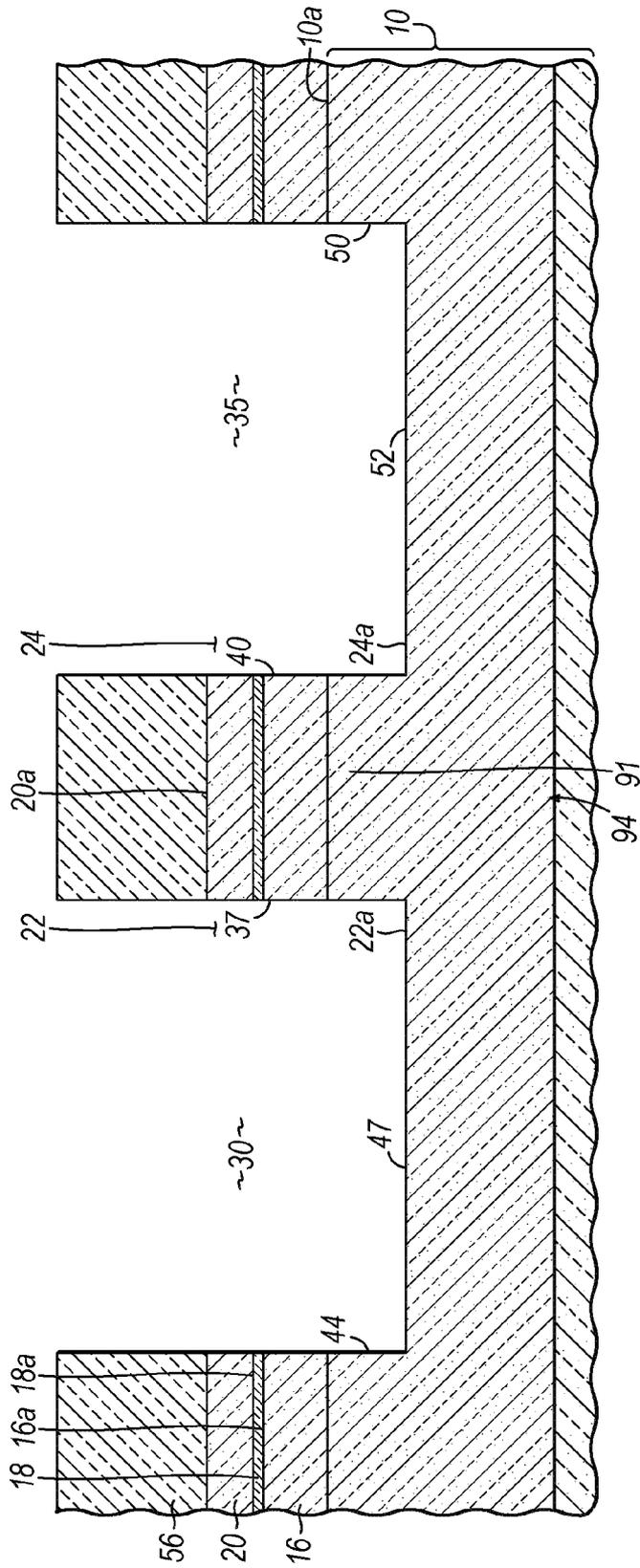


FIG. 2

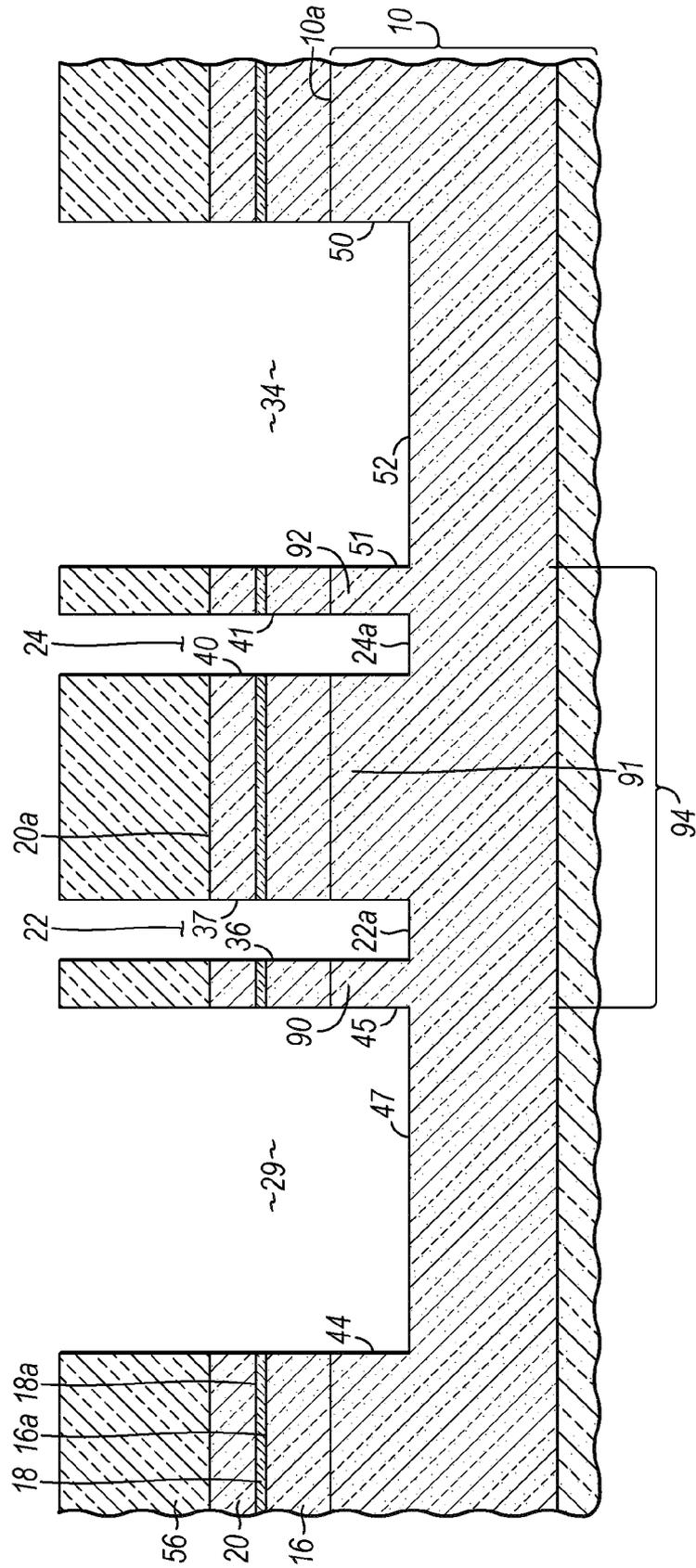


FIG. 2A

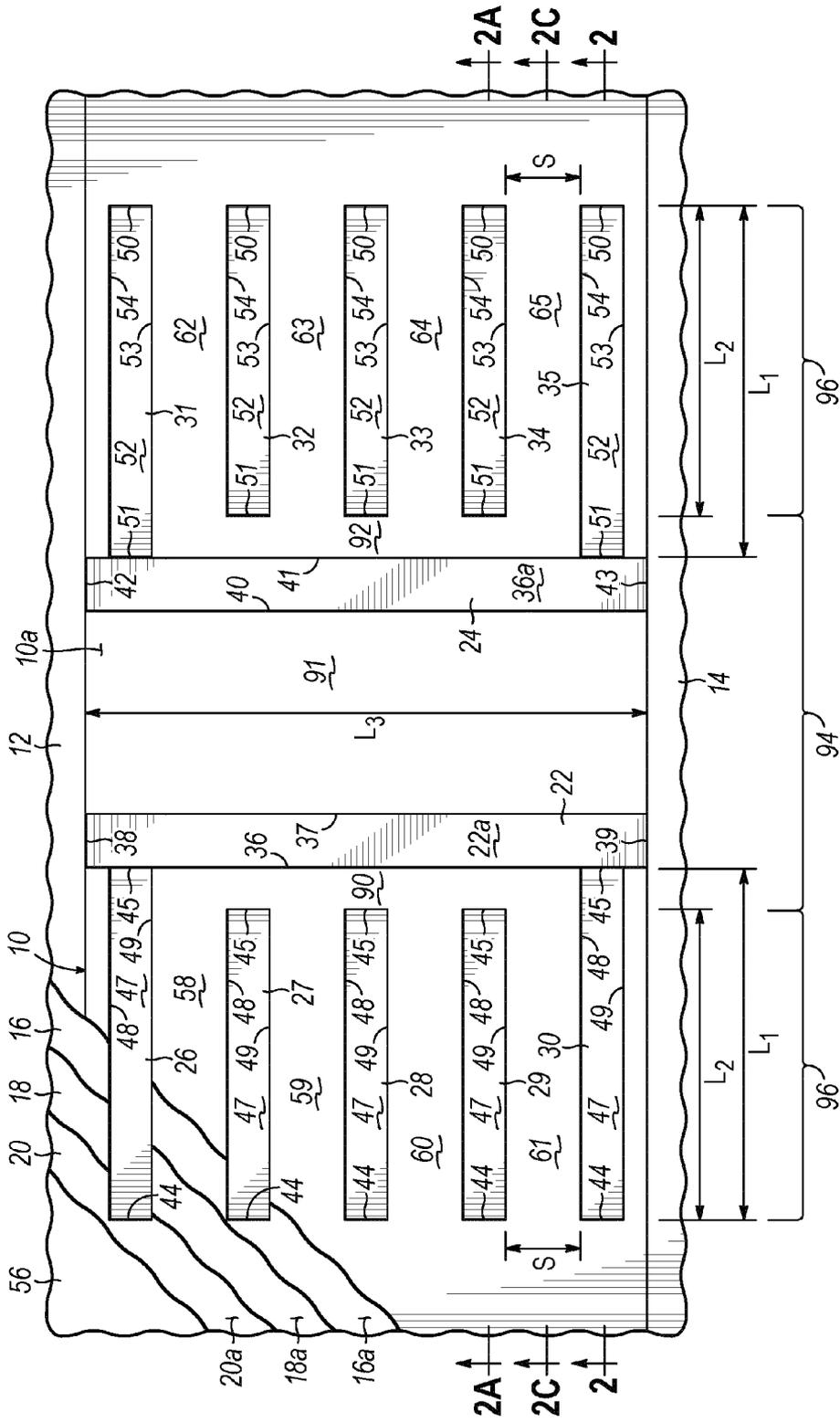


FIG. 2B

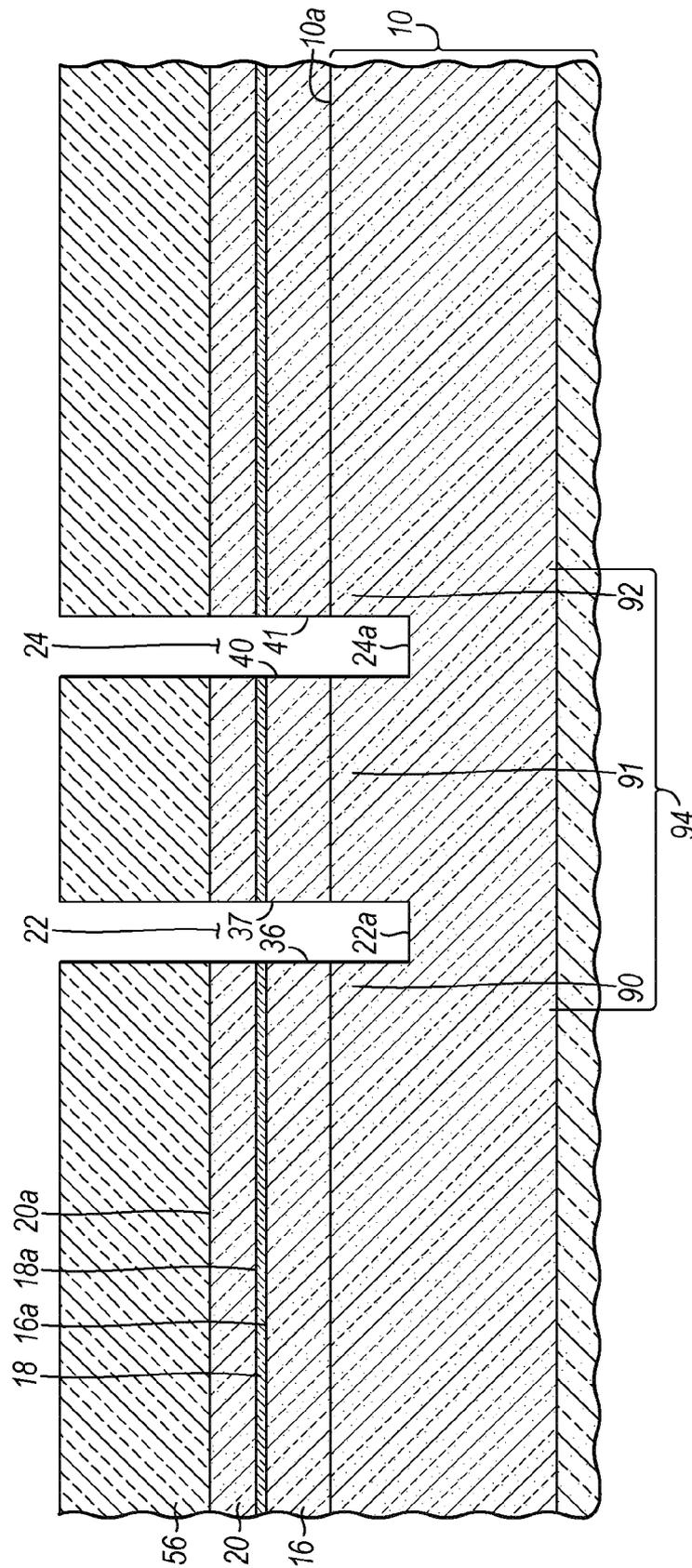


FIG. 2C

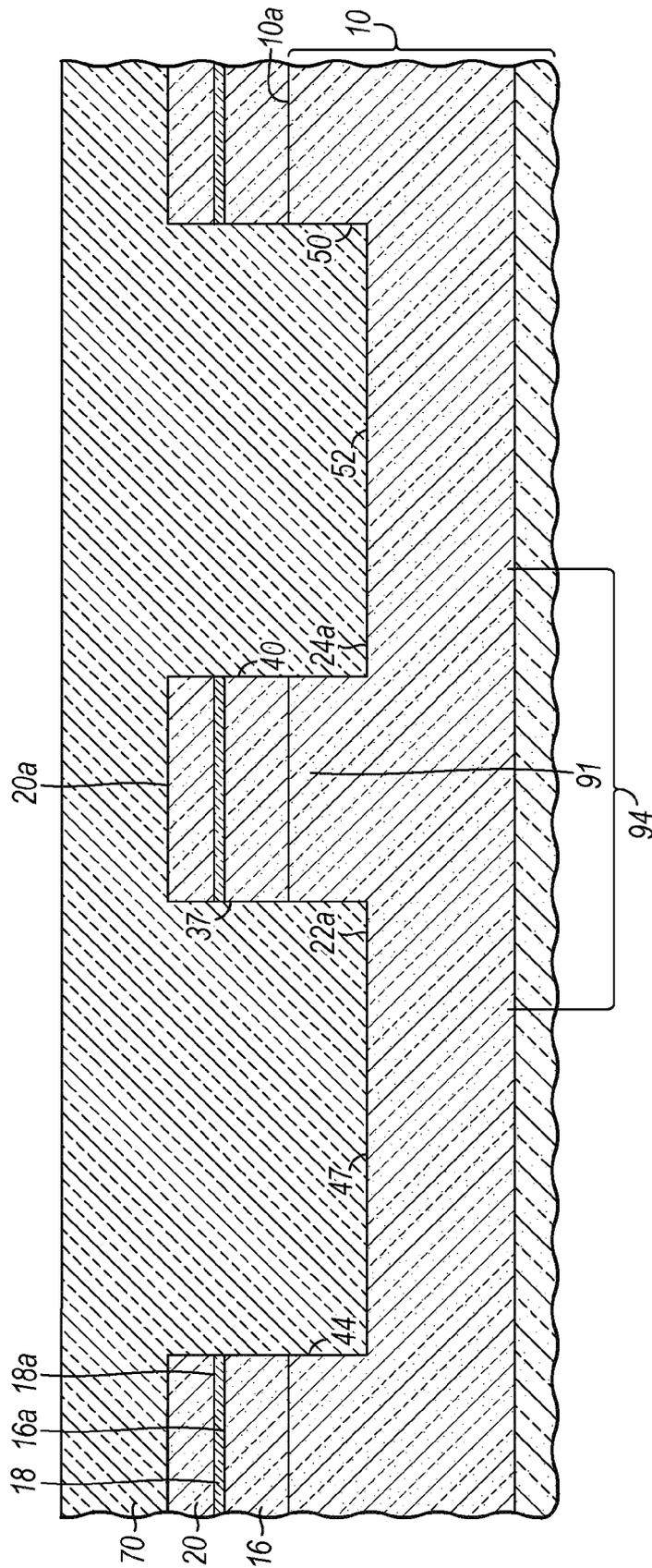


FIG. 3

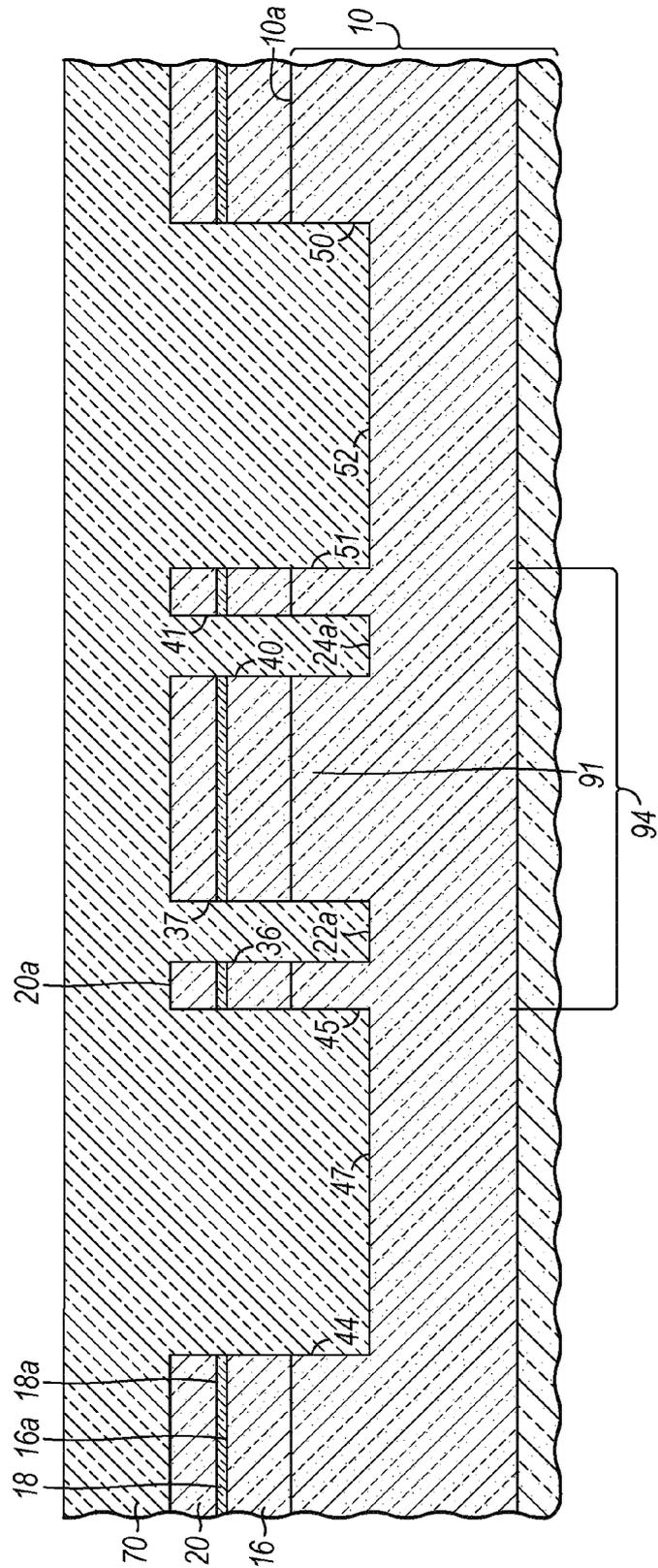


FIG. 3A

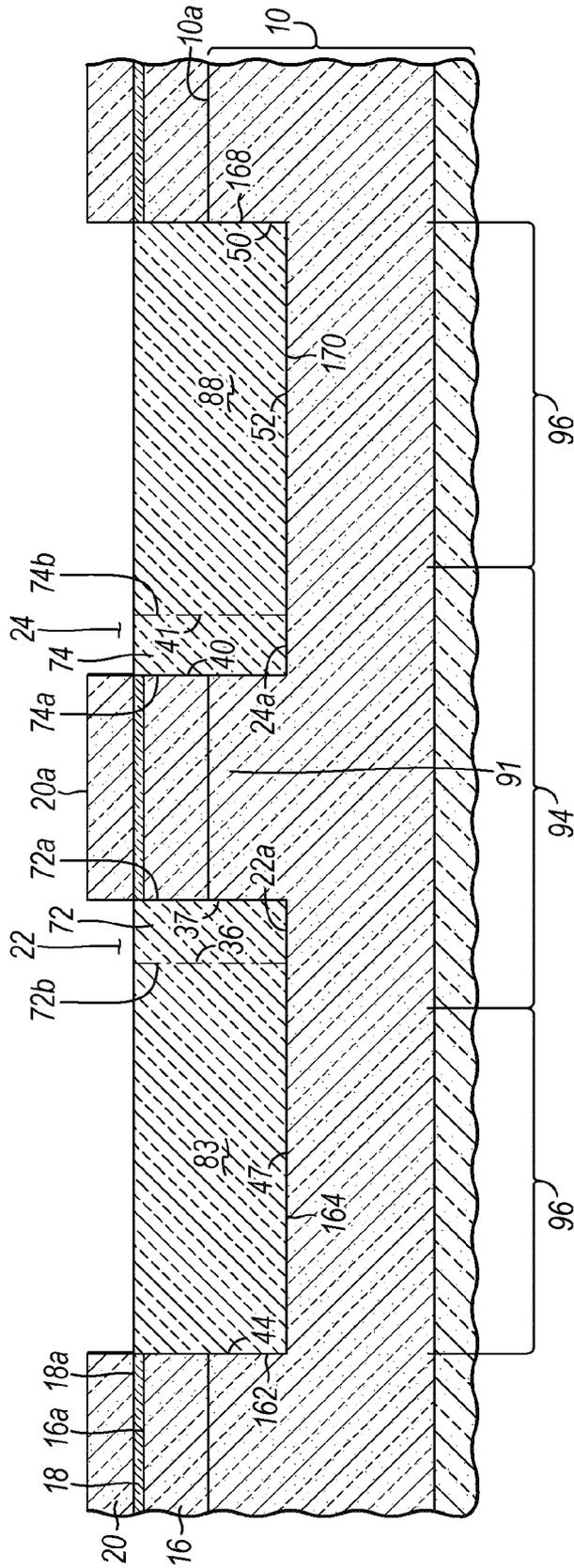


FIG. 4

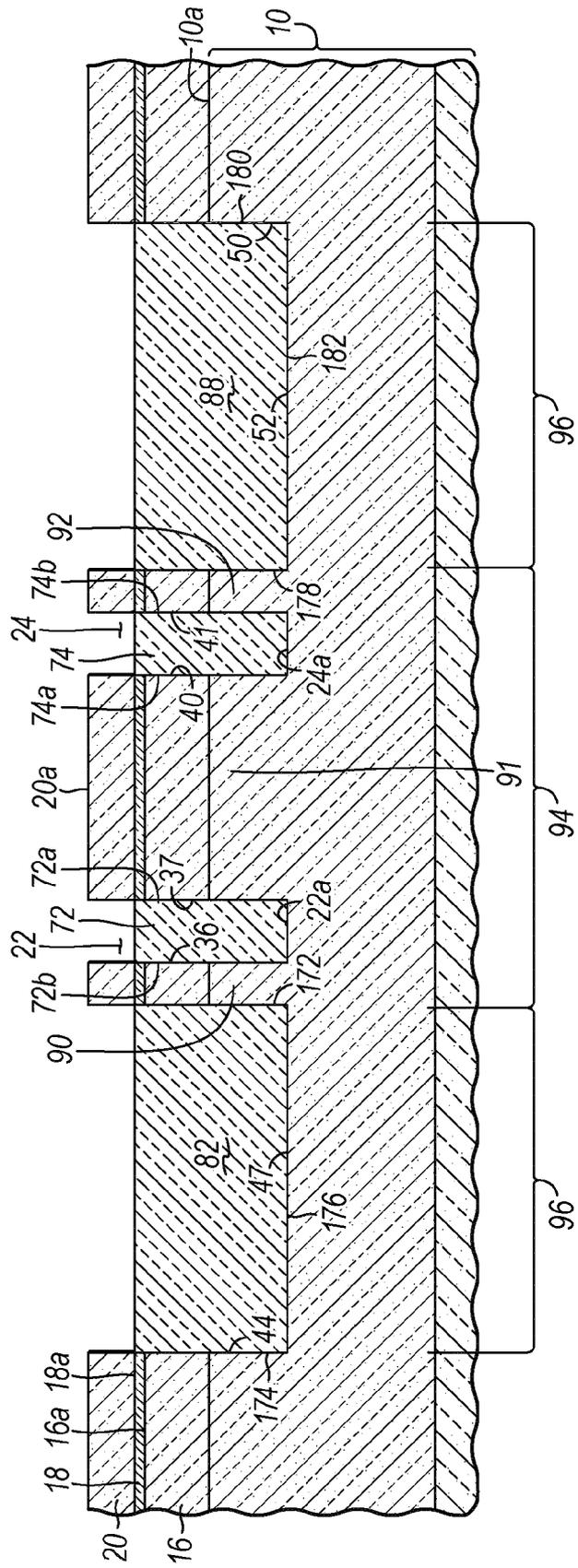


FIG. 4A

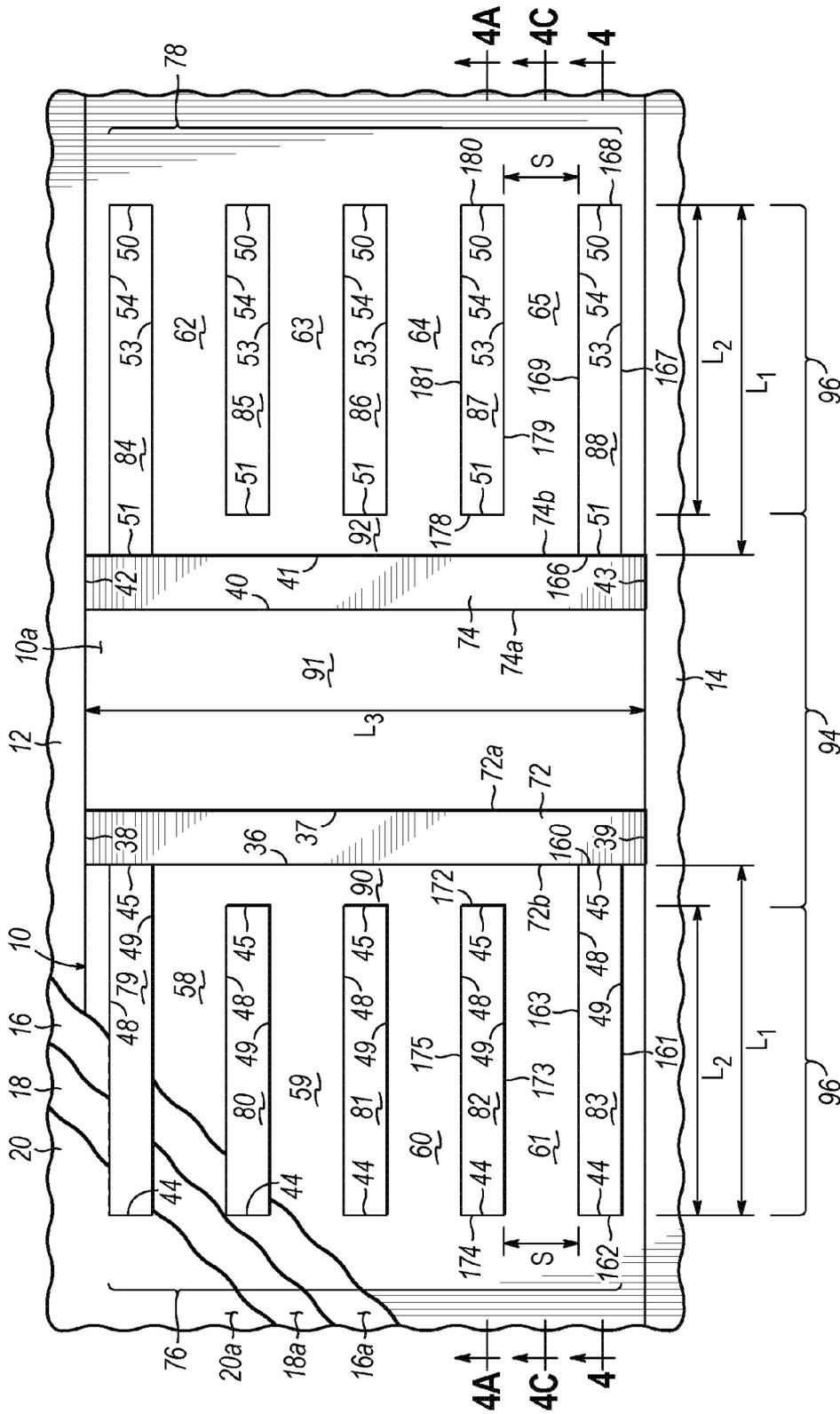


FIG. 4B

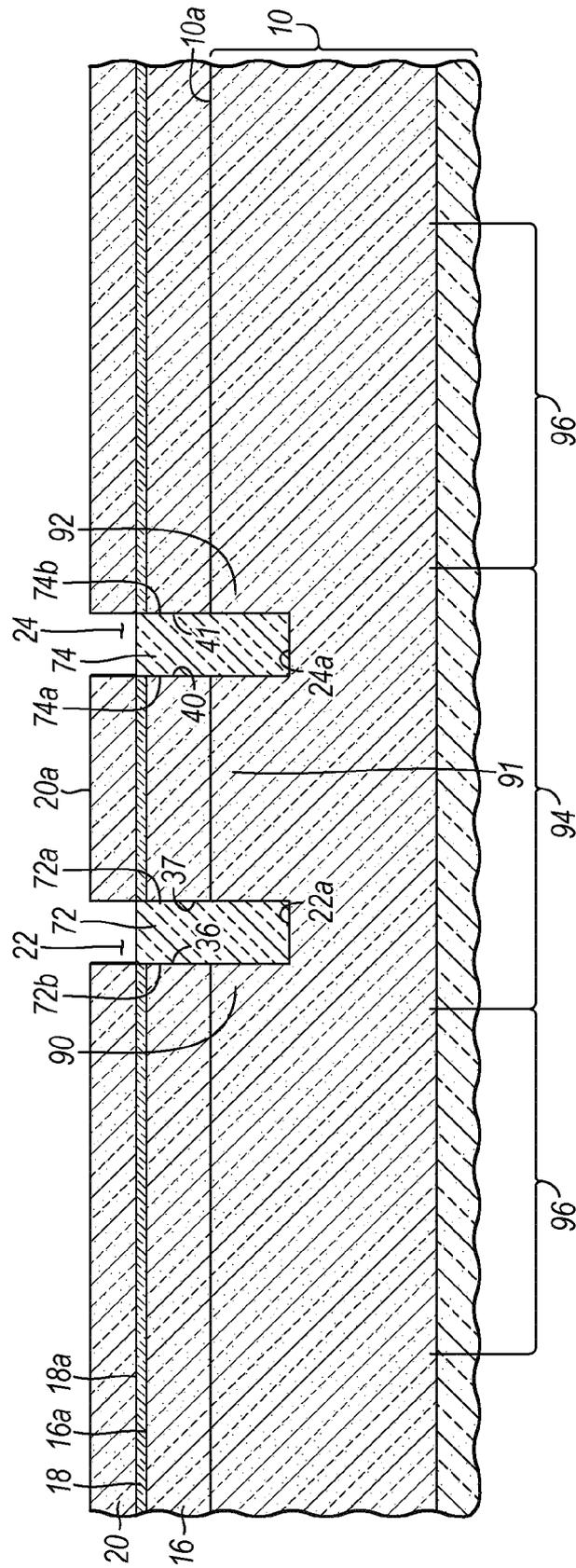


FIG. 4C

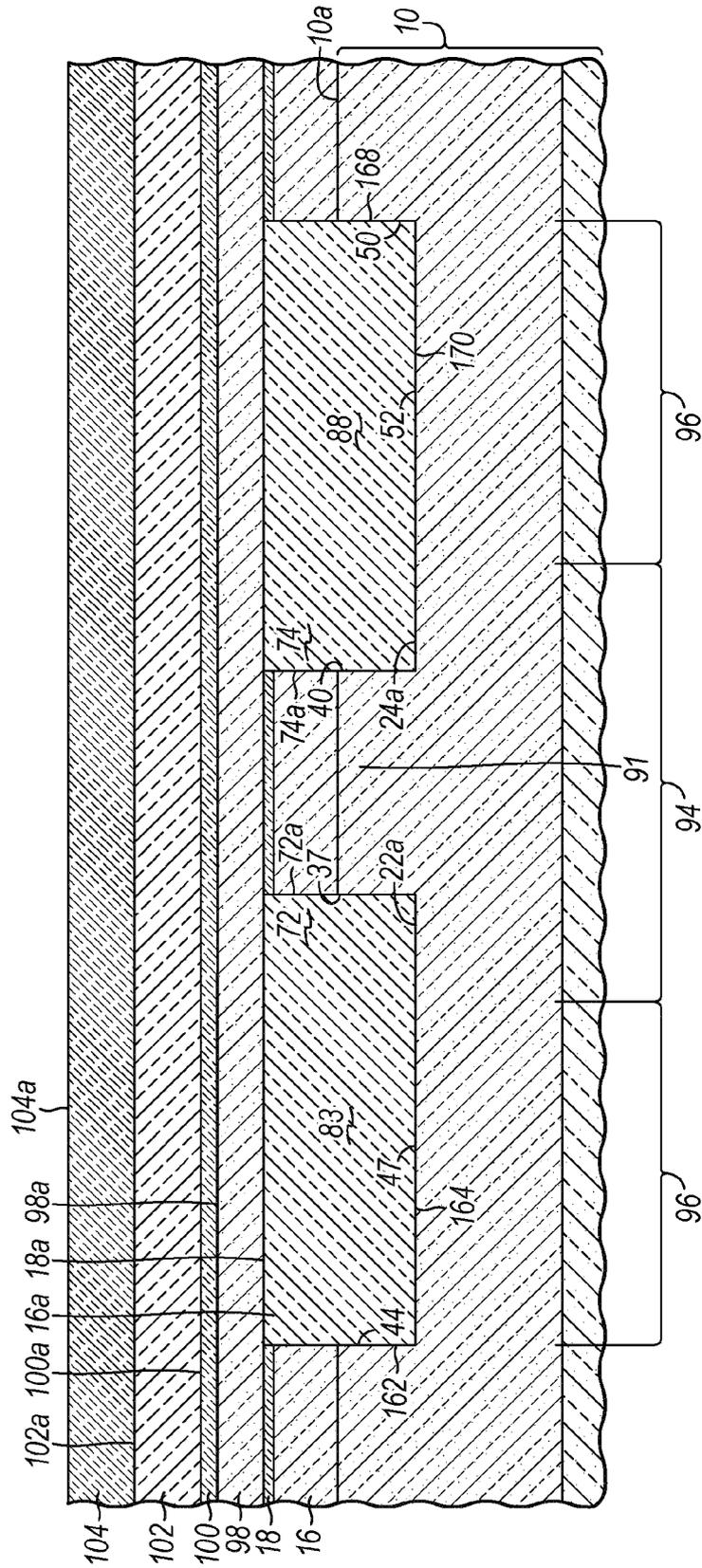


FIG. 5



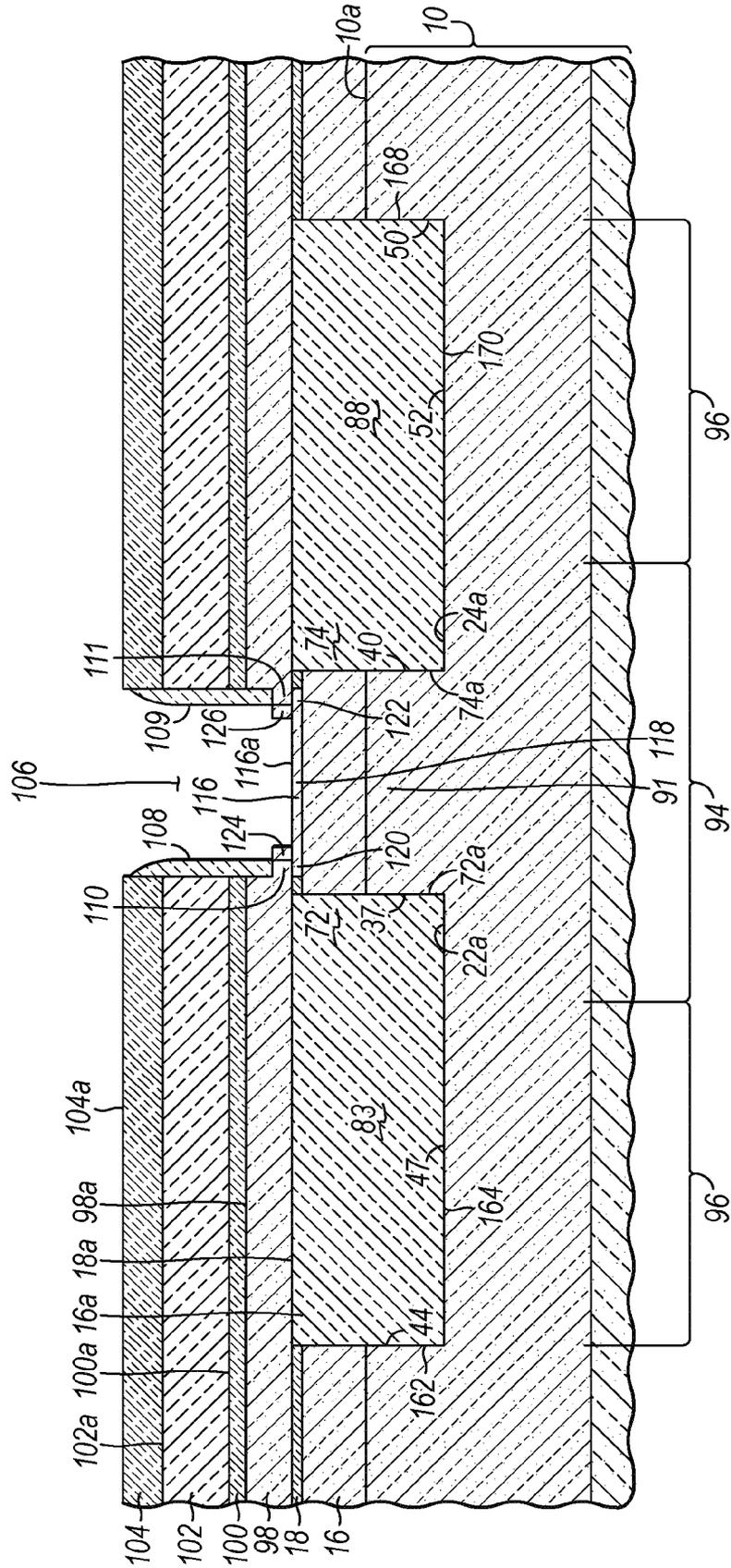


FIG. 7

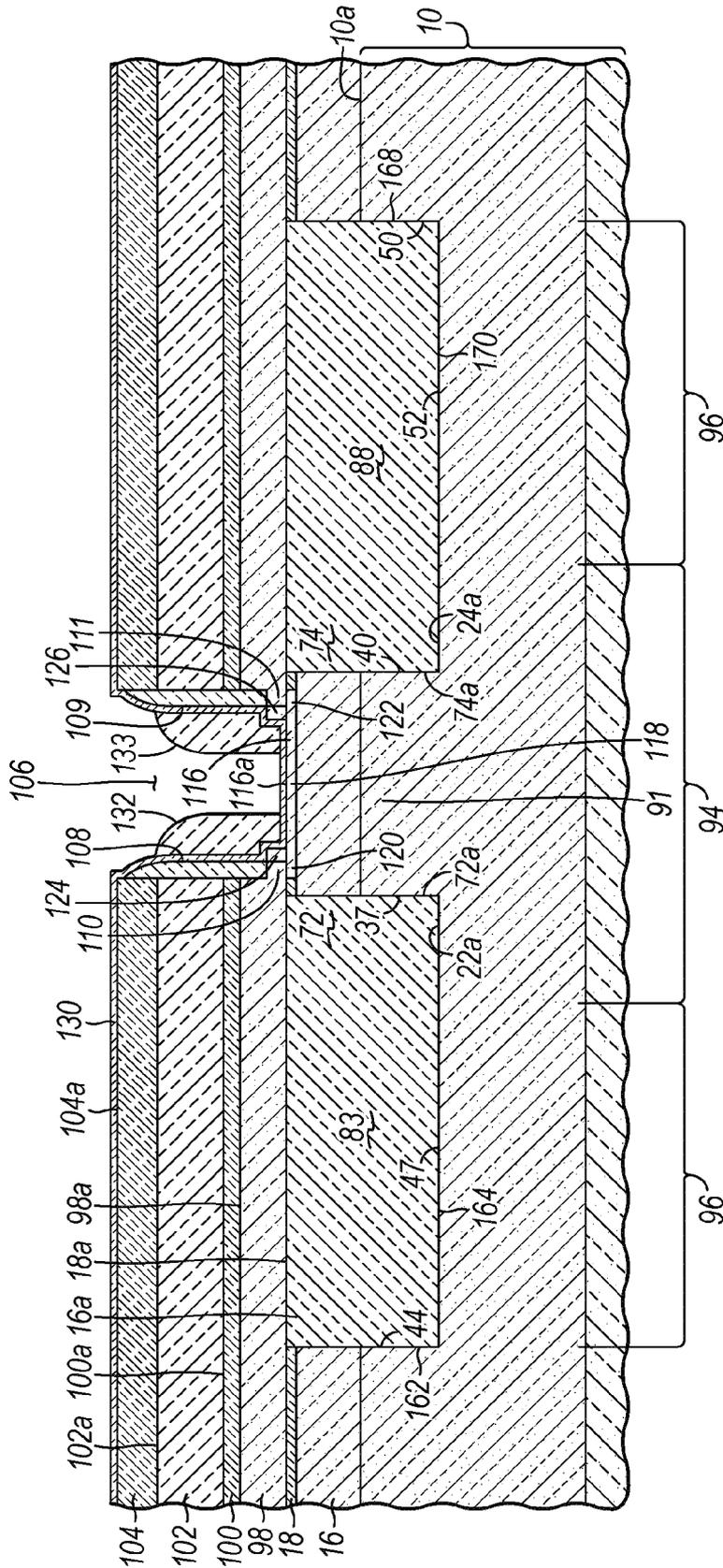


FIG. 8



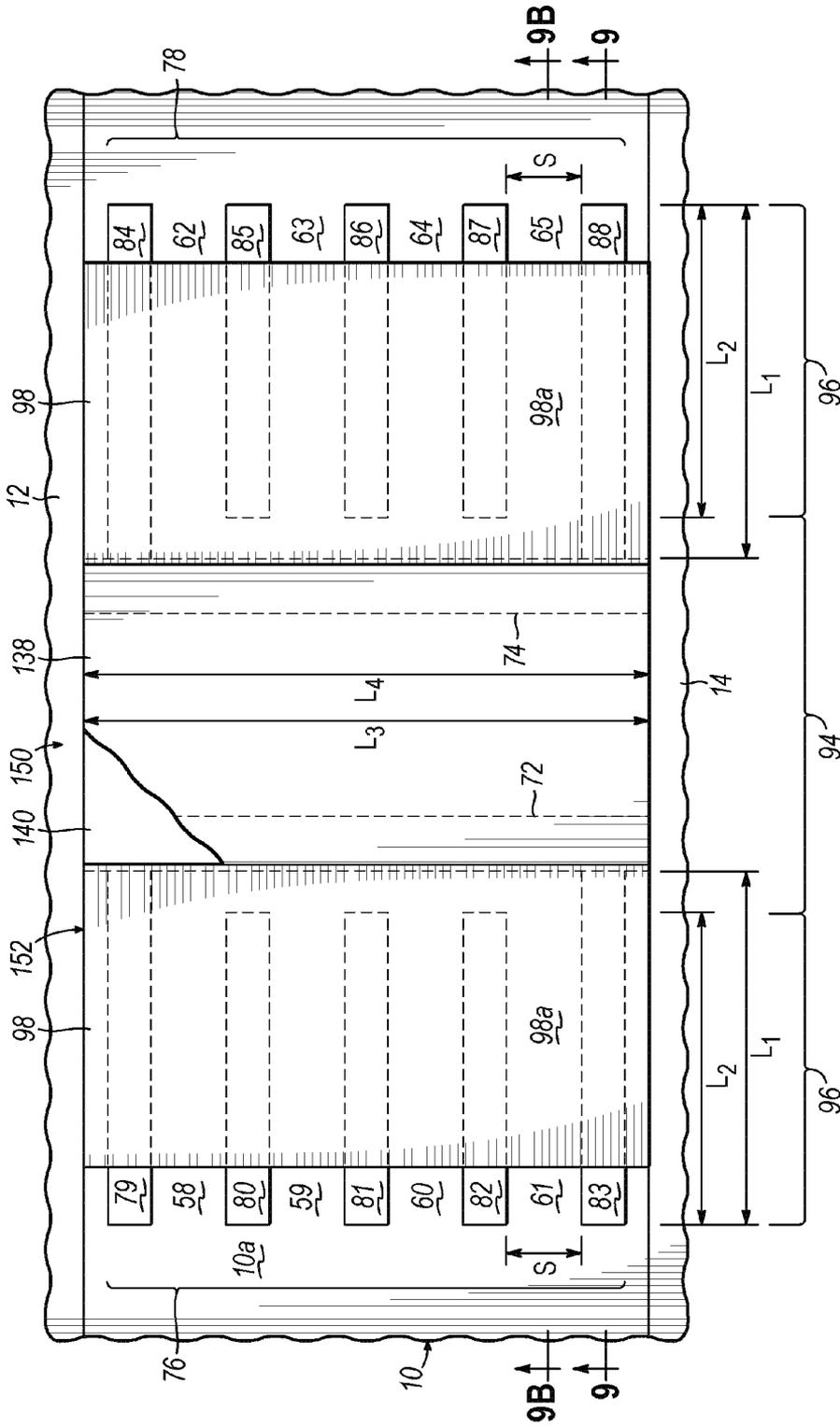


FIG. 9A

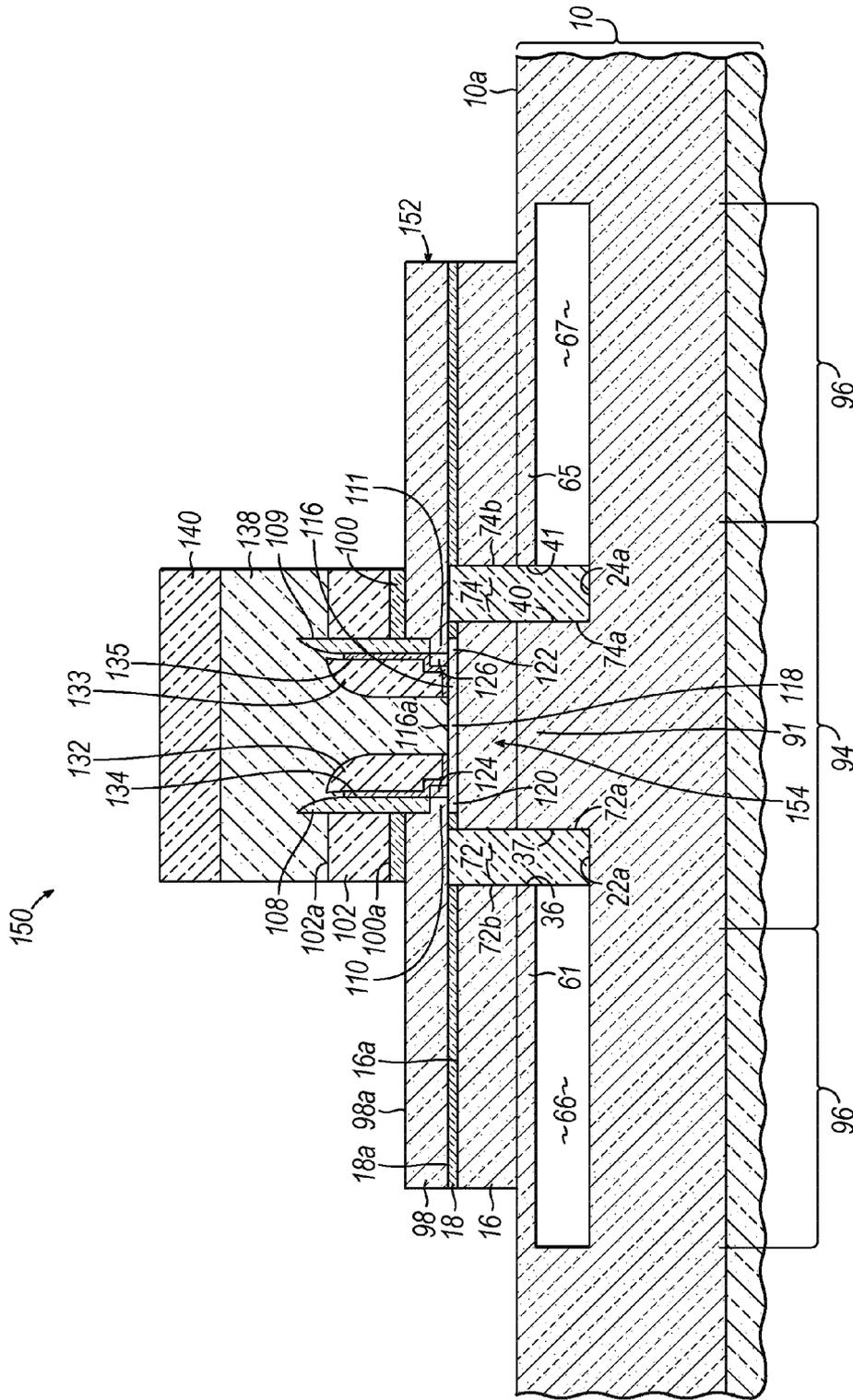


FIG. 9B

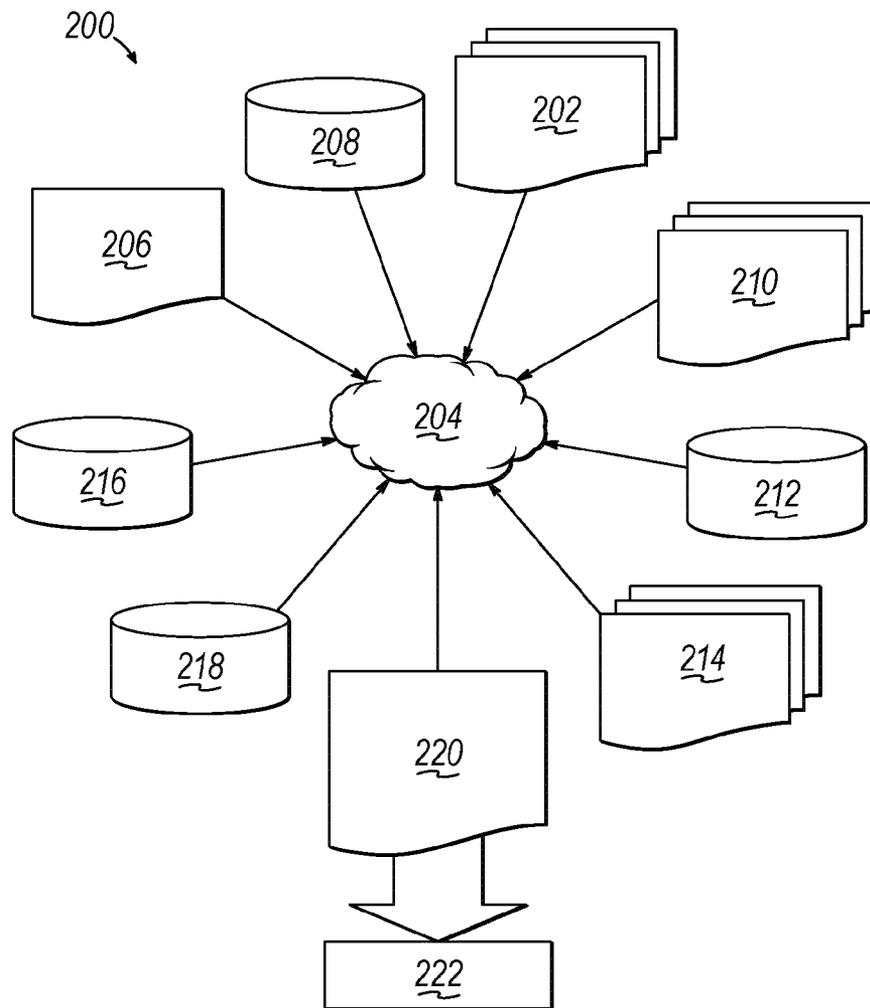


FIG. 10

## ISOLATION SCHEME FOR BIPOLAR TRANSISTORS IN BICMOS TECHNOLOGY

### BACKGROUND

The invention relates generally to semiconductor device fabrication and, in particular, to bipolar junction transistors, fabrication methods for bipolar junction transistors, and design structures for a bipolar junction transistor.

Bipolar junction transistors are typically found in demanding types of integrated circuits, especially integrated circuits destined for high-frequency applications. One specific application for bipolar junction transistors is in radiofrequency integrated circuits (RFICs), which are found in wireless communications systems, power amplifiers in cellular telephones, and other varieties of high-speed integrated circuits. Bipolar junction transistors may also be combined with complementary metal-oxide-semiconductor (CMOS) field effect transistors in bipolar complementary metal-oxide-semiconductor (BiCMOS) integrated circuits, which take advantage of the positive characteristics of both transistor types in the construction of the integrated circuit.

A bipolar junction transistor is a three-terminal electronic device that includes three semiconductor regions, namely an emitter, a base, and a collector. An NPN bipolar junction transistor includes two regions of n-type semiconductor material constituting the emitter and collector, and a region of p-type semiconductor material sandwiched between the two regions of n-type semiconductor material to constitute the base. A PNP bipolar junction transistor has two regions of p-type semiconductor material constituting the emitter and collector, and a region of n-type semiconductor material sandwiched between two regions of p-type semiconductor material to constitute the base. Generally, the differing conductivity types of the emitter, base, and collector form a pair of p-n junctions, namely a collector-base junction and an emitter-base junction. A voltage applied across the emitter-base junction of a bipolar junction transistor controls the movement of charge carriers that produce charge flow between the collector and emitter regions.

Improved device structures, fabrication methods, and design structures are needed for bipolar junction transistors that enhance device performance.

### SUMMARY

In an embodiment of the invention, a method is provided for fabricating a bipolar junction transistor. The method includes forming a collector region in a substrate, forming an intrinsic base layer on the collector region, and forming a plurality of trenches extending into the substrate. The trenches have a length and are arranged with a pitch transverse to the length such that each adjacent pair of the trenches is separated by a respective section of the substrate. The trenches are at least partially filling with an electrical insulator to define a plurality of isolation structures. The method further includes forming an emitter of the bipolar junction transistor coupled by the intrinsic base layer with a portion of the collector region. The emitter has a length transversely oriented relative to the length of the trenches.

In an embodiment of the invention, a device structure is provided for a bipolar junction transistor. The device structure includes a collector region in a substrate and a plurality of isolation structures extending into the substrate. The isolation structures are comprised of an electrical insulator, have a length, and are arranged with a pitch transverse to the length such that each adjacent pair of the isolation structures is

separated by a respective section of the substrate. The device structure further includes an intrinsic base on a portion of the collector region and an emitter on the intrinsic base. The emitter has a length transversely oriented relative to the length of the isolation structures.

In an embodiment of the invention, a hardware description language (HDL) design structure is encoded on a machine-readable data storage medium. The HDL design structure comprises elements that, when processed in a computer-aided design system, generates a machine-executable representation of a device structure for a bipolar junction transistor. The HDL design structure includes a collector region in a substrate and a plurality of isolation structures extending into the substrate. The isolation structures are comprised of an electrical insulator, have a length, and are arranged with a pitch transverse to the length such that each adjacent pair of the isolation structures is separated by a respective section of the substrate. The design structure further includes an intrinsic base on a portion of the collector region and an emitter on the intrinsic base. The emitter has a length transversely oriented relative to the length of the isolation structures. The HDL design structure may comprise a netlist. The HDL design structure may also reside on storage medium as a data format used for the exchange of layout data of integrated circuits. The HDL design structure may reside in a programmable gate array.

### BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWINGS

The accompanying drawings, which are incorporated in and constitute a part of this specification, illustrate various embodiments of the invention and, together with a general description of the invention given above and the detailed description of the embodiments given below, serve to explain the embodiments of the invention.

FIGS. 1-9 are cross-sectional views of a portion of a substrate at successive fabrication stages of a processing method for fabricating a device structure in accordance with an embodiment of the invention.

FIG. 2A is a cross-sectional view of a different portion of the substrate at the fabrication stage of FIG. 2.

FIG. 2B is a top view of the substrate in which FIG. 2 is generally taken along line 2-2 and FIG. 2A is taken generally along line 2A-2A.

FIG. 2C is a cross-sectional view taken generally along line 2C-2C in FIG. 2B.

FIG. 3A is a cross-sectional view similar to FIG. 2A at the fabrication stage of FIG. 3.

FIG. 4A is a cross-sectional view of the different portion of the substrate at the fabrication stage of FIG. 4.

FIG. 4B is a top view of the substrate in which FIG. 4 is generally taken along line 4-4 and FIG. 4A is taken generally along line 4A-4A.

FIG. 4C is a cross-sectional view taken generally along line 4C-4C in FIG. 4B.

FIG. 9A is a top view of the substrate at the fabrication stage of FIG. 9.

FIG. 9B is a cross-sectional view taken generally along line 9B-9B in FIG. 9A.

FIG. 10 is a flow diagram of a design process used in semiconductor design, manufacture, and/or test.

### DETAILED DESCRIPTION

With reference to FIG. 1 and in accordance with an embodiment of the invention, a substrate 10 may be any

suitable bulk substrate comprising a semiconductor material that a person having ordinary skill in the art would recognize as suitable for forming an integrated circuit. For example, substrate **10** may be comprised of a wafer of a monocrystalline silicon-containing material, such as single crystal silicon with a (100) crystal lattice orientation. The semiconductor material comprising substrate **10** may be lightly doped with an impurity to alter its electrical properties and may also include an optional epitaxial layer.

Trench isolation regions **12, 14** (FIG. 2B) are formed in the substrate. The trench isolation regions **12, 14** are discontinuous and arranged as parallel structures. The trench isolation regions **12, 14** may be isolation structures formed by a shallow trench isolation (STI) technique that relies on a lithography and dry etching process to define closed-bottomed trenches in substrate **10**, deposit an electrical insulator to fill the trenches, and planarize the electrical insulator relative to the top surface **10a** of the substrate **10** using a chemical mechanical polishing (CMP) process. The dielectric may be comprised of an oxide of silicon, such as densified tetraethylorthosilicate (TEOS) deposited by chemical vapor deposition (CVD).

The conductivity of the substrate **10** near the top surface **10a** is modified by introducing an electrically-active dopant, such as an impurity species from Group V of the Periodic Table (e.g., phosphorus (P), arsenic (As), or antimony (Sb)) effective to impart an n-type conductivity in which electrons are the majority carriers and dominate the electrical conductivity of the host semiconductor material. In one embodiment, separate ion implantations of n-type impurity species may be used to introduce the dopant at different depths in the substrate and, thereafter, an anneal may activate the impurity species and alleviate implantation damage. One implantation may be a high-current ion implantation followed by a lengthy, high temperature thermal anneal that dopes a surface layer of the substrate **10** before an optional epitaxial layer is formed. Another implantation may comprise a selectively implanted collector (SIC). An anneal may be used to cause the dopant of this implantation to diffuse laterally and vertically such that a surface layer of the substrate **10** becomes impurity doped and, as a result, is structurally and electrically continuous with the more deeply-doped layer from the initial high-current ion implantation.

An intrinsic base layer **16**, which is comprised of a material suitable for forming an intrinsic base of a bipolar junction transistor, is formed a continuous additive layer on a top surface **10a** of substrate **10**. In the representative embodiment, the intrinsic base layer **16** directly contacts the top surface **10a** of the substrate **10** and also directly contacts a top surface of the trench isolation regions **12, 14**. Because trench isolation regions are absent over regions of the substrate **10** laterally bounded on two sides only by the trench isolation regions **12, 14**, the intrinsic base layer **16** is of a uniform thickness where in direct contact with the top surface **10a** of substrate **10** and comprises single crystal semiconductor material.

The intrinsic base layer **16** may be comprised of a semiconductor material, such as silicon-germanium (SiGe) including silicon (Si) and germanium (Ge) in an alloy with the silicon content ranging from 95 atomic percent to 50 atomic percent and the germanium content ranging from 5 atomic percent to 50 atomic percent. The germanium content of the intrinsic base layer **16** may be uniform or the germanium content of intrinsic base layer **16** may be graded or stepped across its thickness. Alternatively, the intrinsic base layer **16** may be comprised of a different semiconductor material, such

as silicon (Si). The intrinsic base layer **16** may be doped with one or more impurity species, such as boron and/or carbon.

Intrinsic base layer **16** may be formed after the trench isolation regions **12, 14** are formed using a low temperature epitaxial (LTE) growth process, such as vapor phase epitaxy (VPE) that may be conducted at a growth temperature ranging from 400° C. to 850° C. The epitaxial growth process may be non-selective as single crystal semiconductor material (e.g., single crystal silicon or SiGe) is epitaxially deposited onto any exposed crystalline surface such as the exposed top surface **10a**. The thickness of the intrinsic base layer **16** may range from about 10 nm to about 600 nm. Layer thicknesses herein are evaluated in a direction normal to the top surface **10a** of substrate **10**.

A base dielectric layer **18** is formed on a top surface **16a** of intrinsic base layer **16** and, in the representative embodiment, directly contacts the top surface **16a**. The base dielectric layer **18**, which reproduces the topography of the underlying intrinsic base layer **16**, may be comprised of an electrical insulator with a dielectric constant (e.g., a permittivity) characteristic of a dielectric material. In one embodiment, the base dielectric layer **18** may be comprised of a high temperature oxide (HTO) deposited using rapid thermal process (RTP) at temperatures of 500° C. or higher. Alternatively, the base dielectric layer **18** may be comprised of oxide formed by a different deposition process, thermal oxidation of silicon (e.g., oxidation at high pressure with steam (HIPOX)), or a combination of these processes.

With reference to FIGS. 2, 2A, 2B, 2C in which like reference numerals refer to like features in FIG. 1 and at a subsequent fabrication stage of the processing method, a sacrificial layer **20** is deposited on the top surface **18a** of the base dielectric layer **18**. In a representative embodiment, the sacrificial layer **20** may be comprised of polysilicon deposited by CVD using either silane or disilane as a silicon source.

Trenches **22, 24** are formed that extend from a top surface **20a** of the sacrificial layer **20** completely through the sacrificial layer **20**, the base dielectric layer **18**, the intrinsic base layer **16**, and into the substrate **10**. Trenches **26, 27, 28, 29, 30** are formed adjacent to trench **22** and trenches **31, 32, 33, 34, 35** are formed adjacent to trench **24**. Trenches **26-35** extend from the top surface **20a** of the sacrificial layer **20** completely through the sacrificial layer **20**, the base dielectric layer **18**, the intrinsic base layer **16**, and into the substrate **10**. Sections **58, 59, 60, 61** of the substrate **10** remain intact between respective adjacent pairs of the trenches **26-30** and sections **62, 63, 64, 65** of the substrate **10** remain between respective adjacent pairs of the trenches **31-35**.

Trench **22** includes an exterior sidewall **36** and an interior sidewall **37** joined to the exterior sidewall **36** by a bottom surface **22a** and sidewalls **38, 39**. Trench **24** includes an interior sidewall **40** and an exterior sidewall **41** joined to the interior sidewall **40** by a bottom surface **24a** and sidewalls **42, 43**. Each of the trenches **26-30** includes an exterior sidewall **44**, an interior sidewall **45**, and a bottom surface **47** and sidewalls **48, 49** joining the exterior sidewall **44** with the interior sidewall **45**. Each of the trenches **31-35** includes an exterior sidewall **50**, an interior sidewall **51**, and a bottom surface **52** and sidewalls **53, 54** joining the exterior sidewall **50** with the interior sidewall **51**. The trenches **22, 24, 26-30**, and **31-35** may each have a shallower depth relative to the top surface **10a** than the depth of the trench isolation regions **12, 14** relative to the same reference plane.

Adjacent pairs of the trenches **26-30** and adjacent pairs of the trenches **31-35** are separated by a spacing, *S*, given by a feature pitch to define respective grating patterns for segmented troughs. The pitch is given by a centerline-to-center-

line distance between the adjacent pairs. The number and feature pitch of the trenches 26-30 and the number and feature pitch of trenches 31-35 are design parameters selected when the trenches 26-35 are formed in the substrate 10.

Trenches 26, 30, 31, and 35 may have a length,  $L_1$ , and trenches 27-29 and 32-34 may be characterized by a length,  $L_2$ , that is shorter than  $L_1$ . Trenches 22, 24 each have a length,  $L_3$ , that may be longer or shorter than one or both of the lengths  $L_1$  or  $L_2$ . In each instance, these lengths represent the longest dimension of the trenches 22, 24, 26-30, and 31-35. A centerline of trench 22 along its length,  $L_3$ , is aligned transverse to respective centerlines of trenches 26-30 along their respective lengths  $L_1$ ,  $L_2$  and is orthogonal to the respective centerlines of trenches 26-30 in the representative embodiment. A centerline of trench 24 along its length,  $L_3$ , is aligned transverse to respective centerlines of trenches 31-35 along their respective lengths  $L_1$ ,  $L_2$  and is orthogonal to the respective centerlines of trenches 31-35 in the representative embodiment. Each of the lengths corresponds to the largest dimension of the respective trenches 22, 24, 27-29 and 32-34 in a plane normal to the top surface 10a.

In the representative embodiment, the respective interior sidewalls 45 of trenches 26 and 30 are coextensive with the exterior sidewall 36 of trench 22 and, thereby, define a continuous open volume. However, the respective interior sidewalls 45 of trenches 27-29 are not coextensive with the exterior sidewall 36 of trench 22 so that a portion 90 of the collector region 94 intervenes between these interior sidewalls 45 and the exterior sidewall 36. In each instance, these lengths represent the longest dimension of the trenches 22 and 26-30.

In the representative embodiment, the respective interior sidewalls 51 of trenches 31 and 35 are coextensive with the exterior sidewall 41 of trench 24 and, thereby, define a continuous open volume. However, the respective interior sidewalls 51 of trenches 32-34 are not coextensive with the exterior sidewall 41 of trench 24 so that a portion 92 of the collector region 94 intervenes between these interior sidewalls 51 and the exterior sidewall 41.

A portion 91 of the collector region 94 is disposed between the interior sidewall 37 of trench 22 and the interior sidewall 40 of trench 24. The portion 91 of the collector region 94 is larger than the portions 90, 92 and is preferably significantly larger than portions 90, 92.

The trenches 22, 24, 26-30, and 31-35 may be formed using photolithography and etching processes. To that end, a mask layer 56 may be applied on the top surface 20a of the sacrificial layer 20. The mask layer 56 may comprise a photoresist that is applied as a fluid by a spin coating process, pre-baked, exposed to a radiation projected through a photomask, baked after exposure, and developed with a chemical developer to form an etch mask that includes a pattern of openings coinciding with the intended locations of the trenches 22, 24, 26-30, and 31-35. The pattern of openings is transferred from the mask layer 56 to the sacrificial layer 20, the base dielectric layer 18, the intrinsic base layer 16, and the substrate 10 to define the trenches 22, 24, 26-30, and 31-35. The etching process may comprise a dry etching process, such as reactive-ion etching (RIE). The etching process, which may be conducted in a single etching step or multiple steps, relies on one or more etch chemistries that remove the materials of the mask layer 56, the sacrificial layer 20, the base dielectric layer 18, the intrinsic base layer 16, and the substrate 10, and may comprise a timed etch. The mask layer 56 is removed at the conclusion of the etching process. If comprised of a photoresist, the mask layer 56 may be removed by ashing or solvent stripping, followed by a conventional cleaning process.

With reference to FIGS. 3, 3A in which like reference numerals refer to like features in FIGS. 2, 2A-2C and at a subsequent fabrication stage of the processing method, a dielectric layer 70 comprised of an electrical insulator is formed that at least partially, and preferably completely, fills the trenches 22, 24, 26-30, and 31-35 with portions of the electrical insulator. The dielectric layer 70 also deposits on the top surface 20a of the sacrificial layer 20.

Dielectric layer 70 may comprise any suitable organic or inorganic dielectric material recognized by a person having ordinary skill in the art. The dielectric layer 70 may be comprised of an electrical insulator, which may be characterized by an electrical resistivity at room temperature of greater than  $10^{10}(\Omega\cdot\text{m})$ . Candidate inorganic dielectric materials for dielectric layer 70 may include, but are not limited to, silicon dioxide ( $\text{SiO}_2$ ), fluorine-doped silicon glass (FSG), and combinations of these dielectric materials. Alternatively, dielectric layer 70 may comprise a low-k dielectric material characterized by a relative permittivity or dielectric constant smaller than the  $\text{SiO}_2$  dielectric constant of approximately 3.9. Candidate low-k dielectric materials for dielectric layer 70 include, but are not limited to, porous and nonporous spun-on organic low-k dielectrics, such as spin-on spun-on aromatic thermoset polymer resins like polyarylenes, porous and nonporous inorganic low-k dielectrics, such as organo-silicate glasses, hydrogen-enriched silicon oxycarbide ( $\text{SiCOH}$ ), and carbon-doped oxides, and combinations of these and other organic and inorganic dielectrics. Dielectric layer 70 may be deposited by any number of techniques including, but not limited to, sputtering, spin-on application, or CVD.

The dielectric material of dielectric layer 70 residing inside the trenches 22, 24, 26-30, and 31-35 may also include sub-surface voids representing empty volumes devoid of solid matter. Such voids may have an effective dielectric constant of approximately unity (about 1.0) and may be filled by air at or near atmospheric pressure, be filled by another gas at or near atmospheric pressure, or contain air or gas below atmospheric pressure (e.g., a partial vacuum) in the completed microelectronic structure. The composite dielectric constant of the dielectric material may be lowered by the introduction of voids.

In one specific embodiment, the dielectric layer 70 may be comprised of an oxide of silicon (e.g.,  $\text{SiO}_2$ ) that may be deposited by low pressure chemical vapor phase deposition (LPCVD) using a silicon source of either silane or a mixture of silane with nitrogen. LPCVD is conducted at subatmospheric pressures, which tends to reduce unwanted gas-phase reactions and improve film thickness uniformity across the substrate 10. For example, the substrate temperature during LPCVD may range from 600° C. to 650° C. and the process chamber pressure during LPCVD may be constrained in a range between 25 Pa and 150 Pa.

With reference to FIGS. 4, 4A, 4B in which like reference numerals refer to like features in FIGS. 3, 3A and at a subsequent fabrication stage of the processing method, the dielectric layer 70 is removed from the top surface 20a of the sacrificial layer 20 but not from within the trenches 22, 24, 26-30, and 31-35. The dielectric layer 70 may be removed from the top surface 20a by a wet etching process or a dry etching process, which may be end-pointed based upon exposure of the sacrificial layer 20 or may alternatively be timed. If the dielectric layer 70 is comprised of an oxide of silicon, then RIE may be employed to remove the dielectric layer 70 from the top surface 20a of sacrificial layer 20. Alternatively, an oxide etch, such as buffered hydrofluoric acid or diluted hydrofluoric acid, may be used to remove the dielectric layer

70. The top surface 20a of the sacrificial layer 20 is exposed after the overlying thickness of the dielectric layer 70 is removed.

The electrical insulator inside trenches 22, 24 defines isolation regions 72, 74, which may be recessed relative to the top surface 20a of the sacrificial layer 20 but are not removed by the etching process. The isolation regions 72, 74 extend through the intrinsic base layer 16 and into the substrate 10 to a depth relative to the top surface 10a that is shallower than the depth of the trench isolation regions 12, 14. Isolation region 72 has boundaries nominally coextensive with the boundaries of trench 22, and isolation region 74 has boundaries nominally coextensive with the boundaries of trench 24. Isolation regions 72, 74 have respective interior sidewalls 72a, 74a and respective exterior sidewalls 72b, 74b.

The isolation regions 72, 74 reproduce the geometrical shape of the respective trenches 22, 24. In one embodiment, the isolation regions 72, 74 may comprise strips of electrical insulator that are aligned parallel to each other, and the isolation regions 72, 74 do not define a closed geometrical shape. In an alternative embodiment, the isolation regions 72, 74 may join or may be joined by additional isolation regions so that the isolation regions 72, 74 form a closed geometrical shape. The isolation regions 72, 74 penetrate to a shallower depth relative to the top surface 10a of the substrate 10 than the trench isolation regions 12, 14. In the representative embodiment, each of the isolation regions 72, 74 has a length nominally equal to length  $L_3$ .

The electrical insulator inside trenches 26-30 defines a plurality of isolation structures 79, 80, 81, 82, 83 that collectively comprise an isolation region 76. The isolation structures 79-83 reproduce the geometrical shape of the trenches 26-30. In one embodiment, the isolation structures 79-83 may comprise strips of electrical insulator that are aligned parallel relative to each other and transverse to a strip of electrical insulator comprising isolation region 72.

Isolation structure 83, which reproduces the geometrical shape of the trench 30, includes sidewalls 160, 161, 162, 163 and a bottom wall 164. Sidewall 160 is coextensive with the exterior sidewall 72b of isolation region 72. Isolation structure 79 includes sidewalls and a base wall similar in geometry and arrangement to those of isolation structure 83. Similarly, isolation structure 88, which reproduces the geometrical shape of the trench 35, includes sidewalls 166, 167, 168, 169 and a bottom wall 170. Sidewall 166 is coextensive with the exterior sidewall 74b of isolation region 74. Isolation structure 84 includes sidewalls and a bottom wall similar in geometry and arrangement to those of isolation structure 88. In the representative embodiment, each of the isolation structures 79, 83, 84, 88 has a length nominally equal to length  $L_1$ .

The electrical insulator inside trenches 31-35 defines a plurality of isolation structures 84, 85, 86, 87, 88 that collectively comprise an isolation region 78. The isolation structures 84-88 reproduce the geometrical shape of the trenches 31-35. In one embodiment, the isolation structures 84-88 may comprise strips of electrical insulator that are aligned parallel relative to each other and transverse to a strip of electrical insulator comprising isolation region 74.

Isolation structure 82, which reproduces the geometrical shape of the trench 29, includes sidewalls 172, 173, 174, 175 and a bottom wall 176. Sidewall 172 is spaced apart from the exterior sidewall 72b of isolation region 72 by a portion 90 of the collector region 94. Isolation structures 80, 81 include sidewalls and a bottom wall similar in geometry and arrangement to those of isolation structure 82. The portion 90 of the collector region 94 extends laterally from isolation structure 79 to isolation structure 83 and, in the transverse direction,

extends from the isolation structures 80-82 to the exterior sidewall 72b of isolation region 72. In the representative embodiment, each of the isolation structures 80-82 has a length nominally equal to length  $L_2$  and, therefore, may be shorter in length than isolation structures 79, 83.

Similarly, isolation structure 87, which reproduces the geometrical shape of the trench 34, includes sidewalls 178, 179, 180, 181 and a bottom wall 182. Sidewall 178 is spaced apart from the exterior sidewall 74b of isolation region 74 by a portion 92 of the collector region 94. Isolation structures 85, 86 include sidewalls and a base wall similar in geometry and arrangement to those of isolation structure 87. The portion 92 of the collector region 94 extends laterally from isolation structure 84 to isolation structure 88 and, in the transverse direction, extends from the isolation structures 85-87 to the exterior sidewall 74b of isolation region 74. In the representative embodiment, each of the isolation structures 85-87 has a length nominally equal to length  $L_2$  and, therefore, may be shorter in length than isolation structures 84, 88.

The collector region 94 is peripherally disposed between the interior sidewalls 172 of the isolation structures 80-82 and the interior sidewalls 178 of the isolation structures 85-87. The portion 91 of the collector region 94 is located between an interior sidewall 72a of isolation region 72 and an interior sidewall 74a of isolation region 74. Only the portions 90, 92 of collector region 94, which are comparatively smaller than the portion 91 of the collector region 94, reside peripherally outside of the isolation regions 72, 74. The isolation structures 79-83 and the isolation structures 84-88 are segmented with additional intervening portions 58-61 and 62-65, respectively, of the semiconductor material of the collector region 94 separating adjacent pairs of the isolation structures 79-88.

A subcollector region 96 is defined as a portion of the substrate 10 that is beneath the isolation regions 76, 78 and that emerges at the top surface 10a of substrate 10 peripherally outside of the isolation regions 76, 78 to permit establishment of electrical contact. The collector region 94 and subcollector region 96 are each doped with the electrically-active dopant from the initial ion implantations (FIG. 1) so that the collector region 94 and subcollector region 96 have the same conductivity type. The isolation regions 72, 74 are disposed peripherally between the isolation regions 76, 78 such that the isolation regions 72, 74 are positioned within the collector region 94.

With reference to FIG. 5 in which like reference numerals refer to like features in FIGS. 4, 4A-4D and at a subsequent fabrication stage of the processing method, the sacrificial layer 20 is partially or completely removed to reduce the height difference between either the top surface 20a of the sacrificial layer 20 or, if the sacrificial layer 20 is completely removed, the top surface 18a of the base dielectric layer 18 and the top surfaces of the isolation regions 72, 74, 76, 78. The sacrificial layer 20 may be at least partially removed by a wet etching process or a dry etching process. In particular, if the sacrificial layer 20 is comprised of polysilicon, the sacrificial layer 20 may be partially or completely removed by an etching process, such as a dry etch process or a wet etch process (e.g., an aqueous mixture of nitric acid ( $\text{HNO}_3$ ) and hydrofluoric acid (HF)). The base dielectric layer 18 may operate as an etch stop for the removal of the sacrificial layer 20 if the materials comprising the sacrificial layer 20 and base dielectric layer 18 are selected such that the sacrificial layer 20 can be selectively etched relative to base dielectric layer 18.

An extrinsic base layer 98 is formed on the top surface 18a of the base dielectric layer 18. In one embodiment, the extrinsic base layer 98 may be comprised of polycrystalline semiconductor material (e.g., polysilicon or polycrystalline SiGe)

deposited by CVD process. If the extrinsic base layer **98** is comprised of SiGe, the concentration of Ge may have a graded or an abrupt profile and may include additional layers, such as a Si cap. The extrinsic base layer **98** may be in situ doped with a concentration of a dopant, such as an impurity species from Group III of the Periodic Table (e.g., boron) effective to impart p-type conductivity. As a consequence of the deposition process and the non-crystalline nature of base dielectric layer **18** on which extrinsic base layer **98** is formed, the entire extrinsic base layer **98** is comprised of polycrystalline semiconductor material. If the sacrificial layer **20** is only partially removed before the extrinsic base layer **98** is deposited and is comprised of, for example, polysilicon, then the remaining thickness of the sacrificial layer **20** is subsumed into the extrinsic base layer **98**. The extrinsic base layer **98** also covers the top surfaces of the isolation regions **72**, **74**, **76**, **78**.

A stack of dielectric layers **100**, **102**, **104** is then formed on the extrinsic base layer **98**. Dielectric layer **100**, which is formed on a top surface **98a** of extrinsic base layer **98**, may directly contact the top surface **98a**. Dielectric layer **102**, which is formed on a top surface **100a** of dielectric layer **100**, may directly contact the top surface **100a**. Dielectric layer **104**, which is formed on a top surface **102a** of dielectric layer **102**, may directly contact the top surface **102a**. Dielectric layer **100** and dielectric layer **104** may be comprised of the same electrical insulator, such as SiO<sub>2</sub> deposited by CVD. Dielectric layer **102** may be comprised of an electrical insulator with a different etch selectivity than dielectric layers **100**, **104**. If the dielectric layers **100**, **104** are comprised of SiO<sub>2</sub>, then dielectric layer **102** may be comprised of silicon nitride (Si<sub>3</sub>N<sub>4</sub>) deposited using CVD.

With reference to FIG. **6** in which like reference numerals refer to like features in FIG. **5** and at a subsequent fabrication stage of the processing method, dielectric layers **100**, **102**, **104** are patterned using photolithography and etching processes to define an emitter opening **106** aligned with the intrinsic base layer **16** overlying the collector region **94**. To that end, a patterned etch mask (not shown) is applied to the dielectric layer **104**. In one embodiment, the etch mask may be a photoresist layer comprised of a sacrificial organic material applied by spin coating to the top surface **104a** of dielectric layer **104**. The photolithography process that patterns the photoresist layer exposes the photoresist to radiation imaged through a photomask and develops the resulting latent feature pattern in the exposed photoresist to define a window at the intended location for the emitter opening **106**. The etching process, which may be RIE, forms the emitter opening **106** in the dielectric layers **100**, **102**, **104** by sequentially removing regions of each of the dielectric layers **100**, **102**, **104** unprotected by the etch mask. The etching process, which may be conducted in a single etching step or multiple steps, relies on one or more etch chemistries that remove the individual dielectric layers **100**, **102**, **104** and may comprise one or more discrete timed or end-pointed etches.

The emitter opening **106** is extended by an etching process, such as RIE, into the extrinsic base layer **98**. The etching process is controlled such that the emitter opening **106** is only partially extended through the thickness of the extrinsic base layer **98**. Specifically, a thickness of the extrinsic base layer **98** is partially removed by the etching process across the surface area of the top surface **98a** that is exposed inside the emitter opening **106** in dielectric layers **100**, **102**, **104**. After etching, the top surface **98a** of extrinsic base layer **98** overlying the collector region **94** is recessed (i.e., in a different plane) relative to a plane containing the top surface **98a** of the extrinsic base layer **98** in masked regions. The extrinsic base

layer **98** overlying the collector region **94** is thinner than the extrinsic base layer **98** outside of the emitter opening **106**, which gives rise to a thickness difference. The etching process may be controlled such that the emitter opening **106** extends approximately half-way through the layer thickness of the extrinsic base layer **98**. Following the conclusion of the etching process, the etch mask is removed. If comprised of photoresist, the etch mask may be removed by oxygen plasma ashing or chemical stripping.

Spacers **108**, **109** are formed on the vertical sidewalls of the layers **98**, **100**, **102**, **104** bounding the emitter opening **106**. The spacers **108**, **109**, which extend vertically to the base of the emitter opening **106**, may directly contact the recessed top surface **98a** of extrinsic base layer **98**. The spacers **108**, **109** may be formed by depositing a conformal layer comprised of an electrical insulator and shaping the conformal layer with an anisotropic etching process, such as a RIE process, that preferentially removes the electrical insulator from horizontal surfaces. At the conclusion of the anisotropic etching process, the spacers **108**, **109** constitute residual electrical insulator residing on the vertical surfaces represented by the coplanar sidewalls of the layers **98**, **100**, **102**, **104**. The spacers **108**, **109** may be comprised of a dielectric material that is an electrical insulator, such as Si<sub>3</sub>N<sub>4</sub> deposited by CVD in which instance the spacers **108**, **109** are composed of the same dielectric material as dielectric layer **102**.

With reference to FIG. **6** in which like reference numerals refer to like features in FIG. **5** and at a subsequent fabrication stage of the processing method, the emitter opening **106**, as narrowed by the presence of the spacers **108**, **109**, is extended in depth completely through the extrinsic base layer **98** over an area aligned with the emitter opening **106**. The extension of the emitter opening **106** may be provided by an anisotropic etching process, such as a RIE process. The etching process removes the material of extrinsic base layer **98** selectively (e.g., at a higher etch rate) to the materials comprising spacers **108**, **109** and base dielectric layer **18**, and stops on the base dielectric layer **18**. Adjacent to the emitter opening **106** and beneath the spacers **108**, **109**, sections **110**, **111** of extrinsic base layer **98** remain at the conclusion of the etching process. The sidewall of section **110** is vertically aligned with the adjacent portion of the sidewall of the spacer **108** bordering the emitter opening **106**. The sidewall of section **111** is vertically aligned with the adjacent portion of the sidewall of the spacer **109** bordering the emitter opening **106**.

The emitter opening **106** is extended in depth through the base dielectric layer **18** by an isotropic etching process, such as a wet chemical etching process. The etching process stops on the intrinsic base layer **16**. The removal of this region of base dielectric layer **18** exposes the top surface **16a** of intrinsic base layer **16** aligned with the emitter opening **106**. The isotropic etching process removes the material of base dielectric layer **18** selectively to the materials comprising the spacers **108**, **109**, the extrinsic base layer **98**, and the intrinsic base layer **16**. If the base dielectric layer **18** is comprised of SiO<sub>2</sub>, the wet chemical etching process may use either dilute hydrofluoric (DHF) or buffered hydrofluoric (BHF) as an etchant. If dielectric layer **104** is comprised of SiO<sub>2</sub> and contingent upon the etching conditions, the isotropic etching process may reduce the thickness of dielectric layer **104**, as shown in the representative embodiment, or may completely remove dielectric layer **104** from dielectric layer **102**.

Cavities **112**, **113** are formed between the sections **110**, **111** of extrinsic base layer **98** and the intrinsic base layer **16** when the base dielectric layer **18** is etched. Specifically, the isotropic etching process causes the base dielectric layer **18** to recede laterally beneath the sections **110**, **111** of extrinsic

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base layer **98** and, more specifically, sidewalls of the base dielectric layer **18** are respectively caused to laterally recede relative to the respective sidewall of the sections **110**, **111**. In the representative embodiment, the sidewalls of the base dielectric layer **18** are each respectively recessed by a distance, *d*, relative to the sidewalls of sections **110**, **111**. The etch bias may be controlled during etching to regulate the lateral recession of the base dielectric layer **18** and, hence, the location of the sidewalls of the base dielectric layer **18** and depth of the cavities **112**, **113**. The sections **110**, **111** of extrinsic base layer **98** are undercut by the cavities **112**, **113** and the cavities **112**, **113** define open spaces between the intrinsic base layer **16** and the extrinsic base layer **98**.

Because the top surface **98a** of extrinsic base layer **98** is recessed before the spacers **108**, **109** are formed, the sections **110**, **111** of extrinsic base layer **98** are thinner than the remainder of extrinsic base layer **98** outside of the vicinity of the emitter opening **106**. For example, the sections **110**, **111** may be one half of the thickness of the remainder of extrinsic base layer **98**, which is nominally equal to the original deposited thickness. The sections **110**, **111** of extrinsic base layer **98** may extend about the perimeter of the emitter opening **106** and may be connected together to form a continuous structure.

With reference to FIG. 7 in which like reference numerals refer to like features in FIG. 6 and at a subsequent fabrication stage of the processing method, a semiconductor layer **116** is formed as an additive layer on the top surface **16a** of the intrinsic base layer **16** and, in the representative embodiment, is directly formed on the top surface **16a**. The semiconductor layer **116** is comprised of semiconductor material deposited by an epitaxy method. The semiconductor material comprising the semiconductor layer **116** may be doped during or following deposition, or may be alternatively undoped. The semiconductor layer **116** may have a different composition than either the intrinsic base layer **16** or the extrinsic base layer **98**.

During the deposition process, the semiconductor material of semiconductor layer **116** nucleates on the semiconductor material of the intrinsic base layer **16** and acquires the crystalline state (e.g., single crystal) of the intrinsic base layer **16** during growth. The deposition conditions are tailored so that there is no deposition on the spacers **108**, **109** and dielectric layer **104** (or dielectric layer **102** if dielectric layer **104** has been previously removed). The thickness of the semiconductor layer **116** measured in a direction normal to its top surface **116a** may be in the range for approximately 4 to 30 nm.

The semiconductor layer **116** includes a central section **118** flanked by peripheral sections **120**, **122**. Peripheral sections **120**, **122**, which are disposed along the outer perimeter or edges of semiconductor layer **116**, respectively occupy the cavities **112**, **113** and define a link electrically and physically coupling the intrinsic base layer **16** and the extrinsic base layer **98**. The peripheral sections **120**, **122** extend laterally from the respective sidewalls of the base dielectric layer **18** toward a centerline of the emitter opening **106**. The peripheral sections **120**, **122** of the semiconductor layer **116** and the extrinsic base layer **98** are in direct physical and electrical contact with each other, as are the peripheral sections **120**, **122** and the top surface **16a** of the intrinsic base layer **16**. Specifically, the peripheral sections **120**, **122** provide a direct connection for current flow between the extrinsic base layer **98** and the intrinsic base layer **16**. The peripheral sections **120**, **122** and the base dielectric layer **18** may have approximately equal layer thicknesses and, preferably, have equivalent layer thicknesses because the cavities **112**, **113** are formed by the lateral recession of base dielectric layer **18** and

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then respectively filled by the peripheral sections **120**, **122**. The central section **118** of the semiconductor layer **116**, which is located outside of the cavities **112**, **113**, is disposed between the unfilled space of the emitter opening **106** and the intrinsic base layer **16**.

The semiconductor material constituting semiconductor layer **116** also grows on the material of the sections **110**, **111** of extrinsic base layer **98** and grows laterally inward as additive regions **124**, **126** of polycrystalline material into the emitter opening **106**. The deposition process is controlled such that the additive regions **124**, **126** project a short distance into the emitter opening **106** so that the emitter opening **106** is not significantly pinched off.

With reference to FIG. 8 in which like reference numerals refer to like features in FIG. 7 and at a subsequent fabrication stage of the processing method, a conformal layer **130** comprised of a dielectric material is deposited and spacers **132**, **133** are formed on the spacers **108**, **109** with conformal layer **130** as an intervening structure. The conformal layer **130** may be formed from a dielectric material that is electrically insulating, such as a thin layer of SiO<sub>2</sub> which may comprise a high temperature oxide (HTO) deposited by rapid thermal process (RTP) at temperatures of 500° C. or higher. Alternatively, the conformal layer **130** may be deposited by a different deposition process. Spacers **132**, **133** are comprised of a dielectric material that is electrically insulating and etches selectively to the dielectric material comprising the conformal layer **130**. For example, the spacers **132**, **133** may be comprised of an electrical insulator, such as Si<sub>3</sub>N<sub>4</sub>, formed by deposition and anisotropic etching in a manner similar to spacers **108**, **109**. A portion of the conformal layer **130** covers the top surface **116a** of the semiconductor layer **116** inside the emitter opening **106**.

With reference to FIGS. 9, 9A, and 9B in which like reference numerals refer to like features in FIG. 8 and at a subsequent fabrication stage of the processing method, a top surface **116a** of the semiconductor layer **116** is exposed by an etching process that removes the material of the conformal layer **130** inside the emitter opening **106** and laterally between the spacers **132**, **133**. The etching process stops on the material constituting semiconductor layer **116**. The etching process may be chemical oxide removal (COR) that removes the material of conformal layer **130**, if comprised of SiO<sub>2</sub>, with minimal undercut beneath the spacers **132**, **134**. A COR process may utilize a mixture flow of hydrogen fluoride (HF) and ammonia (NH<sub>3</sub>) in a ratio of 1:10 to 10:1 and may be performed at reduced pressures (e.g., about 1 mTorr to about 100 mTorr) and at approximately room temperature.

Portions of conformal layer **130** residing on dielectric layer **104** and the remnant of dielectric layer **104** are also removed by the etching process to reveal the top surface **102a** of dielectric layer **102**. An optional HF chemical cleaning procedure may follow the etching process. Spacers **134**, **135** are formed from portions of the conformal layer **130** shielded during the performance of the etching process by the spacers **132**, **133** and are respectively disposed between the spacers **108**, **109** and the spacers **132**, **133**.

An emitter **138** of a bipolar junction transistor **150** is formed in the emitter opening **106**. The non-conductive spacers **108**, **109** and **132-135** encircle or surround the emitter **138** for electrically isolating the emitter **138** from the extrinsic base layer **98**. The emitter **138** indirectly contacts the intrinsic base layer **16** because of the intervening semiconductor layer **116**. A dielectric cap **140** may be optionally formed on a head of the emitter **138** and may be comprised of an electrical insulator such as Si<sub>3</sub>N<sub>4</sub>.

The emitter **138** of the bipolar junction transistor **150** may be formed from a layer of a heavily-doped semiconductor material that is deposited and then patterned using lithography and etching processes. For example, the emitter **138** may be formed from polysilicon deposited by CVD or LPCVD and heavily doped with a concentration of a dopant, such as an impurities species from Group V of the Periodic Table, such as phosphorus (P), arsenic (As), to impart n-type conductivity. The heavy-doping level reduces the resistivity of the polysilicon and may be introduced by in situ doping that adds a dopant gas, such as phosphine or arsine, to the CVD reactant gases.

The lithography process forming the emitter **138** from the layer of heavily-doped semiconductor material may utilize photoresist and photolithography to form an etch mask that protects only a strip of the heavily-doped semiconductor material registered with the emitter opening **106**. An etching process that stops on the material of layer **102** is selected to shape the emitter **138** from the protected strip of heavily-doped semiconductor material. The mask is subsequently removed to exposes the top surface **102a** of dielectric layer **102**.

The emitter **138** is electrically and physically coupled with the intrinsic base layer **16** by the semiconductor layer **116**. The bottom part of the emitter **138**, which is located inside the emitter opening **106**, directly contacts the top surface **116a** of the semiconductor layer **116** and indirectly contacts the top surface **16a** of intrinsic base layer **16** due to the intervening semiconductor layer **116**. The head of the emitter **138** protrudes out of the emitter opening **106** and includes lateral arms that partially overlap with the top surface **102a** of dielectric layer **102**. While depicted as flat in the representative embodiment, the top surface of the head of emitter **138** may include a divot.

The emitter **138** has a length,  $L_4$ , with a centerline that is transverse relative to respective centerlines of isolation structures **79-83** (and also relative to respective centerlines of trenches **26-30**) along their respective lengths  $L_1$ ,  $L_2$  and is orthogonal to the respective centerlines of isolation structures **79-83** in the representative embodiment. Similarly, the centerline of the length,  $L_4$ , of emitter **138** is aligned transverse relative to respective centerlines of isolation structures **84-88** (and also relative to respective centerlines of trenches **31-35**) along their respective lengths  $L_1$ ,  $L_2$  and is orthogonal to the respective centerlines of isolation structures **84-88** in the representative embodiment. The length,  $L_4$ , of the emitter **138** corresponds to its largest dimension in a plane normal to the top surface **10a**.

Dielectric layers **100**, **102** are patterned using the same etch mask used to form the emitter **138** and the optional dielectric cap **140**, and an etching process, such as RIE, with suitable etch chemistries. The etch mask is removed after shaping the dielectric layers **100**, **102**.

The footprint of a bipolar junction transistor **150** on substrate **10** is fully defined by using conventional photolithography and etching processes to pattern the layers **16**, **18**, **98**, **100**, **102**. Layers **16**, **18**, **98** are patterned to define an extrinsic base **152** of the bipolar junction transistor **150** from extrinsic base layer **98** and an intrinsic base **154** of the bipolar junction transistor **150** from intrinsic base layer **16**. An etch mask is applied for use in a patterning process that relies on an etching process, such as a RIE process, with respective etch chemistries appropriate to etch the layers **16**, **18**, **98**. Following the etching process, the etch mask is removed.

In one embodiment, the etching process patterning layers **16**, **18**, **98** may partially or completely remove portions of the intrinsic base layer **16** between the base dielectric layer **18**

and sections **58-61** and may partially or completely remove portions of the intrinsic base layer **16** between the base dielectric layer **18** and sections **62-65** of substrate **10** to form cavities, such as the representative cavities **66**, **67** visible in FIG. **9B**. Cavity **66** operates to undercut the extrinsic base layer **98** and base dielectric layer **18** between the isolation structures **82**, **83** and is bounded vertically between section **61** of the substrate **10** and the base dielectric layer **18**. Cavity **67** operates to undercut the extrinsic base layer **98** and base dielectric layer **18** between the isolation structures **87**, **88** and is bounded vertically between section **65** of the substrate **10** and the base dielectric layer **18**. In the representative embodiment, cavity **66** extends across the entire distance (i.e., the width of section **61**) between the neighboring isolation structures **82**, **83**, and cavity **67** extends across the entire distance (i.e., the width of section **65**) between the neighboring isolation structures **87**, **88**. Cavity **66** may extend to the sidewall **72a** of isolation region **72** and cavity **67** may extend to the sidewall **74a** of isolation region **74**. The isolation regions **72**, **74** operate to prevent etching of the collector region **94**. Similar cavities (not shown) may be formed by removing the intrinsic based layer **16** between adjacent pairs of isolation structures **79-82** and adjacent pairs of isolation structures **84-87**.

However, the embodiments of the invention are not so limited because undercutting provided by the etching process may not remove all of the material of layer **16** between the adjacent pairs of isolation structures **79-83** and between the adjacent pairs of isolation structures **84-88**, but may instead only extend partially across the width and length of the sections **58-61** and sections **62-65**.

After patterning, the bipolar junction transistor **150** has a vertical architecture in which the intrinsic base **154** is located between the emitter **138** and the collector region **94**, and the emitter **138**, the intrinsic base **154**, and the collector region **94** are vertically arranged. One p-n junction is defined at the interface between the emitter **138** and the intrinsic base **154**. Another p-n junction is defined at the interface between the collector region **94** and the intrinsic base **154**.

The conductivity types of the semiconductor material constituting the emitter **138** and the semiconductor materials constituting extrinsic base **152** and intrinsic base **154** are opposite. The semiconductor material of the intrinsic base **154**, which may be  $\text{Si}_x\text{Ge}_{1-x}$  doped with boron and/or carbon, may have a narrower band gap than the materials (e.g., silicon) of the emitter **138** and collector region **94**, in which case the bipolar junction transistor **150** includes a Si/SiGe heterojunction. The bipolar junction transistor **150** may comprise either an NPN device or a PNP device contingent upon the conductivity types of the emitter **138**, intrinsic base **154**, and collector region **94**.

The isolation regions **76**, **78** peripherally flanking the collector **94** replace shallow trench isolations that would otherwise be present in conventional constructions. The elimination of the shallow trench isolations eliminates facets from the intrinsic base layer **16** because the conventional layer thickness differential is eliminated. More specifically, the isolation regions **76**, **78** are formed after the intrinsic base layer **16** is deposited, whereas the shallow trench isolations are formed in conventional constructions before the intrinsic base layer **16** is formed. Removing the facets from the active device region for the bipolar junction transistor **150** add more freedom in device design and layout, removes limitations on device area and scaling, and makes the bipolar junction transistor **150** generally flatter in topography to facilitate photolithography processes used in its fabrication.

During the front-end-of-line (FEOL) portion of the fabrication process, the device structure of the bipolar junction transistor **150** is replicated across at least a portion of the surface area of the substrate **10**. In BiCMOS integrated circuits, complementary metal-oxide-semiconductor (CMOS) transistors (not shown) are formed using other regions of the substrate **10**. As a result, both bipolar and CMOS transistors are available on the same substrate **10**.

Standard silicidation and standard back-end-of-line (BEOL) processing follows, which includes formation of contacts and wiring for the local interconnect structure, and formation of dielectric layers, via plugs, and wiring for an interconnect structure coupled by the interconnect wiring with the bipolar junction transistor **150**, as well as other similar contacts for additional device structures like bipolar junction transistor **150** and CMOS transistors (not shown) included in other circuitry fabricated on the substrate **10**. Other active and passive circuit elements, such as diodes, resistors, capacitors, varactors, and inductors, may be fabricated on substrate **10** and available for use in the BiCMOS integrated circuit.

FIG. **10** shows a block diagram of an exemplary design flow **200** used for example, in semiconductor IC logic design, simulation, test, layout, and manufacture. Design flow **200** includes processes, machines and/or mechanisms for processing design structures or devices to generate logically or otherwise functionally equivalent representations of the design structures and/or devices described above and shown in FIGS. **9**, **9A**, **9B**. The design structures processed and/or generated by design flow **200** may be encoded on machine-readable transmission or storage media to include data and/or instructions that when executed or otherwise processed on a data processing system generate a logically, structurally, mechanically, or otherwise functionally equivalent representation of hardware components, circuits, devices, or systems. Machines include, but are not limited to, any machine used in an IC design process, such as designing, manufacturing, or simulating a circuit, component, device, or system. For example, machines may include: lithography machines, machines and/or equipment for generating masks (e.g. e-beam writers), computers or equipment for simulating design structures, any apparatus used in the manufacturing or test process, or any machines for programming functionally equivalent representations of the design structures into any medium (e.g. a machine for programming a programmable gate array).

Design flow **200** may vary depending on the type of representation being designed. For example, a design flow **200** for building an application specific IC (ASIC) may differ from a design flow **200** for designing a standard component or from a design flow **200** for instantiating the design into a programmable array, for example a programmable gate array (PGA) or a field programmable gate array (FPGA) offered by Altera® Inc. or Xilinx® Inc.

FIG. **10** illustrates multiple such design structures including an input design structure **202** that is preferably processed by a design process **204**. Design structure **202** may be a logical simulation design structure generated and processed by design process **204** to produce a logically equivalent functional representation of a hardware device. Design structure **202** may also or alternatively comprise data and/or program instructions that when processed by design process **204**, generate a functional representation of the physical structure of a hardware device. Whether representing functional and/or structural design features, design structure **202** may be generated using electronic computer-aided design (ECAD) such as implemented by a core developer/designer. When encoded

on a machine-readable data transmission, gate array, or storage medium, design structure **202** may be accessed and processed by one or more hardware and/or software modules within design process **204** to simulate or otherwise functionally represent an electronic component, circuit, electronic or logic module, apparatus, device, or system such as those shown in FIGS. **9**, **9A**, **9B**. As such, design structure **202** may comprise files or other data structures including human and/or machine-readable source code, compiled structures, and computer-executable code structures that when processed by a design or simulation data processing system, functionally simulate or otherwise represent circuits or other levels of hardware logic design. Such data structures may include hardware-description language (HDL) design entities or other data structures conforming to and/or compatible with lower-level HDL design languages such as Verilog and VHDL, and/or higher level design languages such as C or C++.

Design process **204** preferably employs and incorporates hardware and/or software modules for synthesizing, translating, or otherwise processing a design/simulation functional equivalent of the components, circuits, devices, or logic structures shown in FIGS. **9**, **9A**, **9B** to generate a netlist **206** which may contain design structures such as design structure **202**. Netlist **206** may comprise, for example, compiled or otherwise processed data structures representing a list of wires, discrete components, logic gates, control circuits, I/O devices, models, etc. that describes the connections to other elements and circuits in an integrated circuit design. Netlist **206** may be synthesized using an iterative process in which netlist **206** is resynthesized one or more times depending on design specifications and parameters for the device. As with other design structure types described herein, netlist **206** may be recorded on a machine-readable data storage medium or programmed into a programmable gate array. The medium may be a non-volatile storage medium such as a magnetic or optical disk drive, a programmable gate array, a compact flash, or other flash memory. Additionally, or in the alternative, the medium may be a system or cache memory, buffer space, or electrically or optically conductive devices and materials on which data packets may be transmitted and intermediately stored via the Internet, or other networking suitable means.

Design process **204** may include hardware and software modules for processing a variety of input data structure types including netlist **206**. Such data structure types may reside, for example, within library elements **208** and include a set of commonly used elements, circuits, and devices, including models, layouts, and symbolic representations, for a given manufacturing technology (e.g., different technology nodes, 32 nm, 45 nm, 90 nm, etc.). The data structure types may further include design specifications **210**, characterization data **212**, verification data **214**, design rules **216**, and test data files **218** which may include input test patterns, output test results, and other testing information. Design process **204** may further include, for example, standard mechanical design processes such as stress analysis, thermal analysis, mechanical event simulation, process simulation for operations such as casting, molding, and die press forming, etc. One of ordinary skill in the art of mechanical design can appreciate the extent of possible mechanical design tools and applications used in design process **204** without deviating from the scope and spirit of the invention. Design process **204** may also include modules for performing standard circuit design processes such as timing analysis, verification, design rule checking, place and route operations, etc.

Design process **204** employs and incorporates logic and physical design tools such as HDL compilers and simulation model build tools to process design structure **202** together with some or all of the depicted supporting data structures along with any additional mechanical design or data (if applicable), to generate a second design structure **220**. Design structure **220** resides on a storage medium or programmable gate array in a data format used for the exchange of data of mechanical devices and structures (e.g. information stored in an IGES, DXF, Parasolid XT, JT, DRG, or any other suitable format for storing or rendering such mechanical design structures). Similar to design structure **202**, design structure **220** preferably comprises one or more files, data structures, or other computer-encoded data or instructions that reside on transmission or data storage media and that when processed by an ECAD system generate a logically or otherwise functionally equivalent form of one or more of the embodiments of the invention shown in FIGS. **9**, **9A**, **9B**. In one embodiment, design structure **220** may comprise a compiled, executable HDL simulation model that functionally simulates the devices shown in FIGS. **9**, **9A**, **9B**.

Design structure **220** may also employ a data format used for the exchange of layout data of integrated circuits and/or symbolic data format (e.g. information stored in a GDSII (GDS2), GL1, OASIS, map files, or any other suitable format for storing such design data structures). Design structure **220** may comprise information such as, for example, symbolic data, map files, test data files, design content files, manufacturing data, layout parameters, wires, levels of metal, vias, shapes, data for routing through the manufacturing line, and any other data required by a manufacturer or other designer/developer to produce a device or structure as described above and shown in FIGS. **9**, **9A**, **9B**. Design structure **220** may then proceed to a stage **222** where, for example, design structure **220**: proceeds to tape-out, is released to manufacturing, is released to a mask house, is sent to another design house, is sent back to the customer, etc.

The method as described above is used in the fabrication of integrated circuit chips. The resulting integrated circuit chips can be distributed by the fabricator in raw wafer form (that is, as a single wafer that has multiple unpackaged chips), as a bare die, or in a packaged form. In the latter case, the chip is mounted in a single chip package (such as a plastic carrier, with leads that are affixed to a motherboard or other higher level carrier) or in a multichip package (such as a ceramic carrier that has either or both surface interconnections or buried interconnections). In any case the chip is then integrated with other chips, discrete circuit elements, and/or other signal processing devices as part of either (a) an intermediate product, such as a motherboard, or (b) an end product. The end product can be any product that includes integrated circuit chips, ranging from toys and other low-end applications to advanced computer products having a display, a keyboard or other input device, and a central processor.

It will be understood that when an element is described as being “connected” or “coupled” to or with another element, it can be directly connected or coupled to the other element or, instead, one or more intervening elements may be present. In contrast, when an element is described as being “directly connected” or “directly coupled” to another element, there are no intervening elements present. When an element is described as being “indirectly connected” or “indirectly coupled” to another element, there is at least one intervening element present.

The terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting of the invention. As used herein, the singular forms

“a”, “an” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms “comprises” and/or “comprising,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

The descriptions of the various embodiments of the present invention have been presented for purposes of illustration, but are not intended to be exhaustive or limited to the embodiments disclosed. Many modifications and variations will be apparent to those of ordinary skill in the art without departing from the scope and spirit of the described embodiments. The terminology used herein was chosen to best explain the principles of the embodiments, the practical application or technical improvement over technologies found in the marketplace, or to enable others of ordinary skill in the art to understand the embodiments disclosed herein.

What is claimed is:

**1.** A device structure for a bipolar junction transistor, the device structure comprising:

a collector region of the bipolar junction transistor in a substrate;

a plurality of first isolation structures extending into the substrate and comprised of an electrical insulator, the first isolation structures having a length and arranged with a first pitch transverse to the length such that each adjacent pair of the first isolation structures is separated by a respective first section of the substrate;

an intrinsic base of the bipolar junction transistor on a first portion of the collector region; and

an emitter of the bipolar junction transistor on the intrinsic base, the emitter having a length transversely oriented relative to the length of the first isolation structures.

**2.** The device structure of claim **1** further comprising:

a first isolation region in the substrate, the first isolation region laterally separated from at least one of the first isolation structures by a second portion of the collector region, and the first isolation region laterally separating the second portion of the collector region from the first portion of the collector region.

**3.** The device structure of claim **2** wherein the first isolation region is comprised of the electrical insulator, and the first isolation region and the first isolation structures extend through the intrinsic base.

**4.** The device structure of claim **2** wherein the first isolation structures are aligned transverse to a length of the first isolation region.

**5.** The device structure of claim **2** wherein at least one of the first isolation structures is not separated by the second portion of the collector region from the first isolation region.

**6.** The device structure of claim **2** further comprising:

a second isolation region in the collector region;

a plurality of second isolation structures extending into the substrate and comprised of the electrical insulator, the second isolation structures having a length and arranged with a second pitch transverse to the length such that each adjacent pair of the second isolation structures is separated by a respective second section of the substrate.

**7.** The device structure of claim **6** wherein the second isolation structures are aligned transverse to a length of the second isolation region.

**8.** The device structure of claim **6** wherein the first isolation structures are separated from the second isolation structures by the first isolation region and the second isolation region.

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9. The device structure of claim 1 wherein the first isolation structures extend through the intrinsic base.

10. The device structure of claim 1 wherein the intrinsic base is vertically positioned between the emitter and the collector region so that the collector region, the intrinsic base, and the emitter have a vertical arrangement. 5

11. The device structure of claim 10 wherein the first isolation structures extend through the intrinsic base.

12. The device structure of claim 1 further comprising: a base dielectric layer on the intrinsic base; and an extrinsic base on the base dielectric layer and the first isolation structures. 10

13. The device structure of claim 12 further comprising: a cavity laterally positioned between an adjacent pair of the first isolation structures and vertically positioned between the base dielectric layer and the substrate. 15

14. The device structure of claim 1 wherein the bipolar junction transistor includes a first heterojunction between the intrinsic base and the emitter, a second heterojunction between the intrinsic base and the collector region, or a combination thereof. 20

15. A hardware description language (HDL) design structure encoded on a machine-readable data storage medium, the HDL design structure comprising elements that when processed in a computer-aided design system generates a machine-executable representation of a bipolar junction transistor, the HDL design structure comprising: 25

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a collector region of the bipolar junction transistor in a substrate;

a plurality of isolation structures extending into the substrate and comprised of an electrical insulator, the isolation structures having a length and arranged with a pitch transverse to the length such that each adjacent pair of the isolation structures is separated by a respective section of the substrate;

an intrinsic base of the bipolar junction transistor on a portion of the collector region; and

an emitter of the bipolar junction transistor on the intrinsic base, the emitter having a length transversely oriented relative to the length of the isolation structures.

16. The HDL design structure of claim 15 wherein the HDL design structure comprises a netlist.

17. The HDL design structure of claim 15 wherein the HDL design structure resides on storage medium as a data format used for the exchange of layout data of integrated circuits.

18. The HDL design structure of claim 15 wherein the HDL design structure resides in a programmable gate array.

19. The HDL design structure of claim 15 wherein the bipolar junction transistor includes a first heterojunction between the intrinsic base and the emitter, a second heterojunction between the intrinsic base and the collector region, or a combination thereof.

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